



GDR NANOMaterials for Energy applications

E L A B O R A T I O N
M E S U R E S M E T R O L O G I E
S I M U L A T I O N S T H E O R I E
A P P L I C A T I O N S

GDR NAME

2nd plenary meeting: October 04-06 2021

Workshop 4: Thermal Management

October 5th 2021

Participants: Younès Ezzahri, Jean-François Robillard, Philippe Ben-Abdallah, Jérémie Drévillon, Nicolas Horny, Karl Joulain, Jérémie Maire, Stéphane Monfray, Elyes Nefzaoui, Stéphane Pailhès, Roberto Simola, Mohamed Amara and Raphael Sommet.

Deuxième rencontre plénière du GDR NAME 04-06 octobre 2021

Outline

● Overview

- Scaling, power, trends, 3D integration, steady-state / transient

● Thermal management for Integrated Circuits (IC)

● Relevant parameters

- Thermal conductivity
- Thermal interface resistance

● Techniques

- Passive: Thermal interface materials

● Applications

- Phase Change Materials devices
- Optical components

● Challenges and perspectives

● Thermotronics

● Overview

- Historic breakthroughs in electronics
- A variety of thermal analogues to the electrical components
- Analogies between linear electrical and thermal components

● Thermal rectifiers and thermal diodes

● Thermal transistors

● Thermal logical gates and memories

● Thermal memristors

● Active control of heat flux

● How about the quantum regime?

● Challenges and perspectives

● Radiative cooling and heating

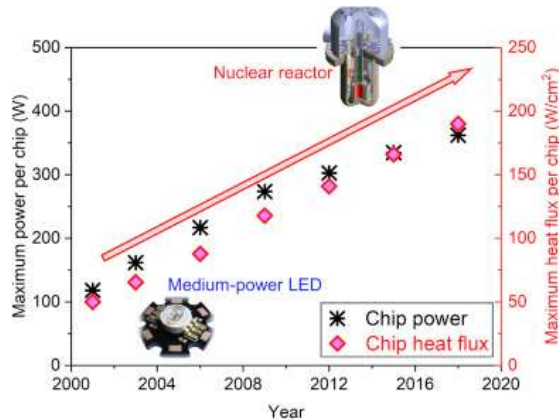
● Principles

● Applications

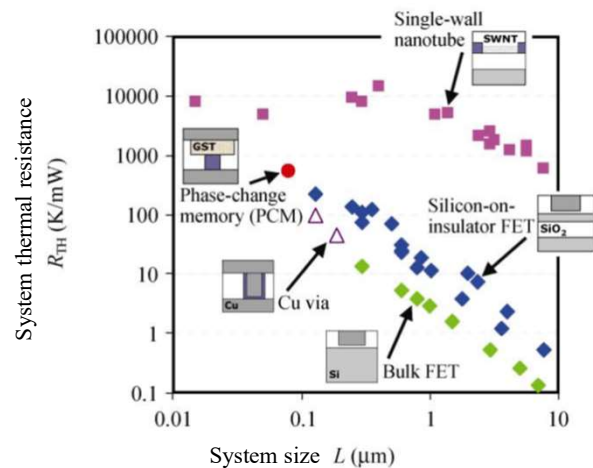
- Daytime radiative cooling
- Nighttime radiative cooling
- Radiative condensers (black silicon)

● Challenges and perspectives

🌞 Orders of magnitude



X.-H. Yang and J. Liu, in Advances in Heat Transfer, 50, 187–300 (2018)

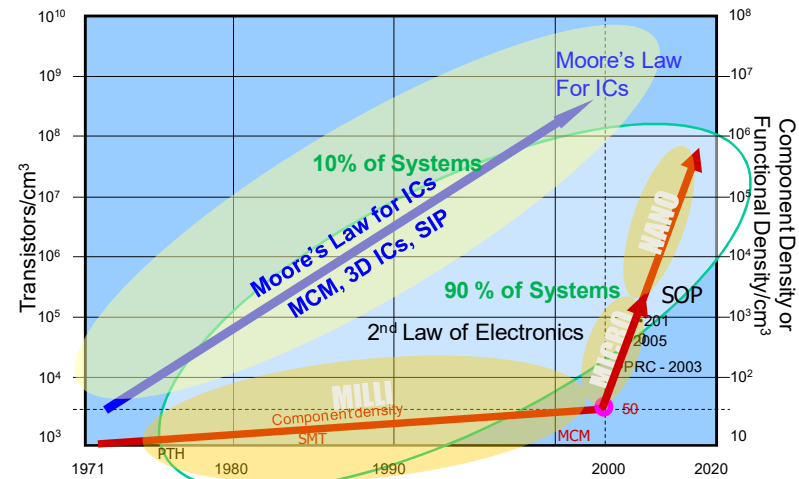


E. Pop, Nano Res (2010) 3: 147–169

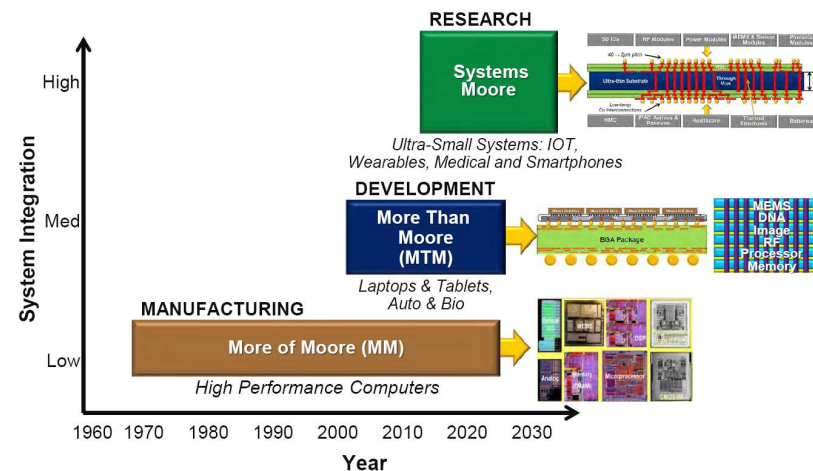
Overview

Trends

From “more Moore” to “system Moore”



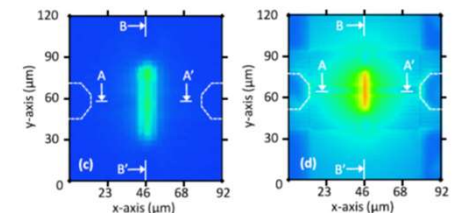
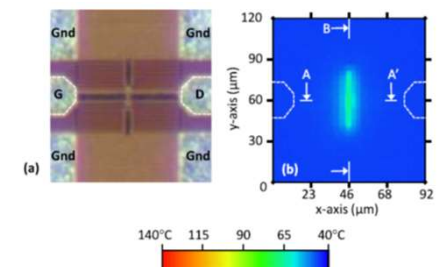
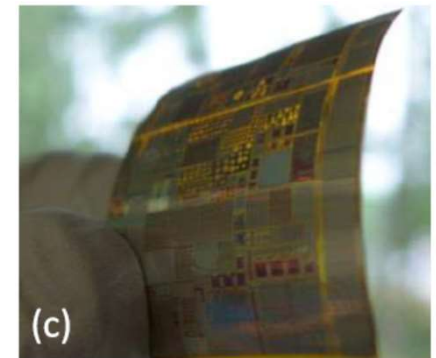
Sources: IBM, Intel



R. Tummala, *System-On-Package (SOP)*, Mc Graw-Hill 2008

Trends

Flexible electronics

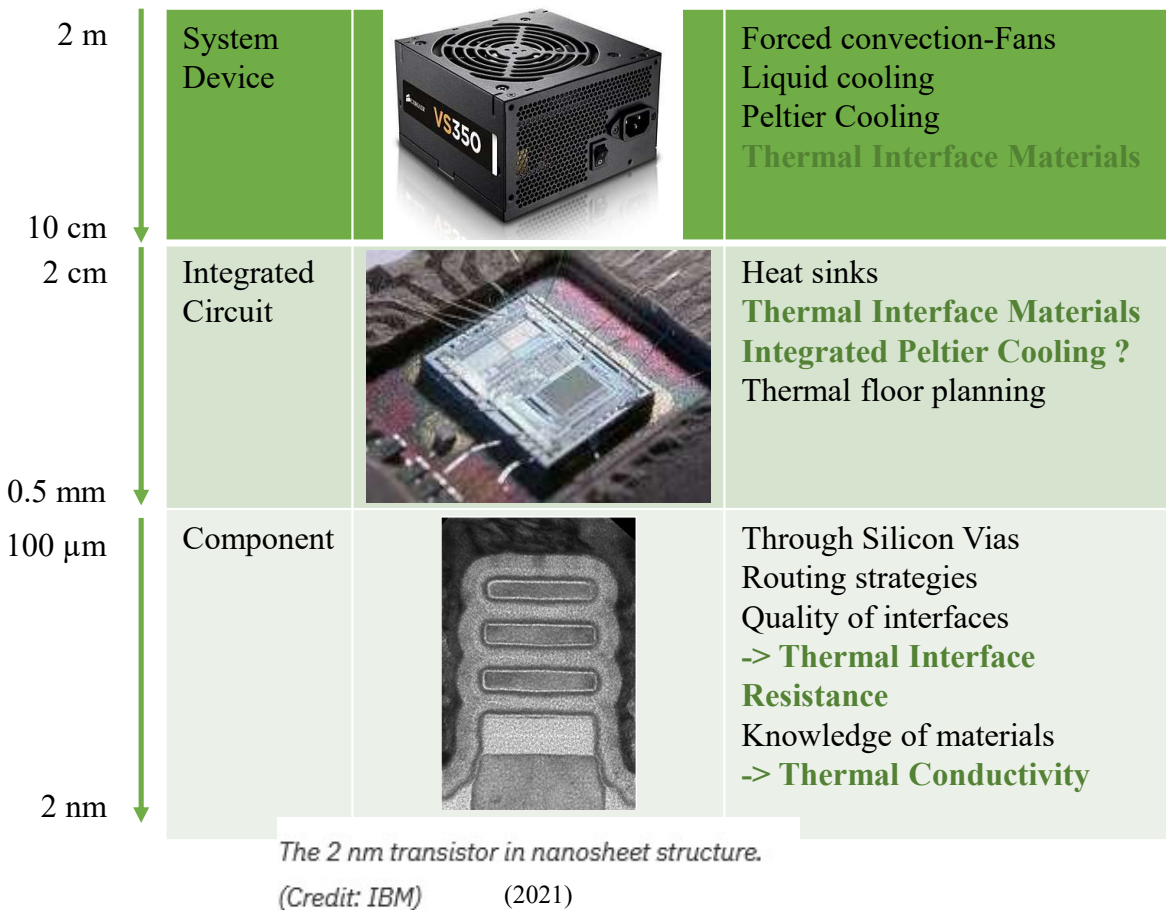


J. Philippe et al. , Journal of the Electron Devices Society, 7, 973 (2019)

Thermal Management for IC

J.-F. Robillard

Relevant scales



Relevant parameters

At component scale, knowledge of
Thermal conductivity (TC)
Thermal boundary resistance (TBR)
 becomes critical for IC design...

Types of management

Active

Peltier
 Forced convection

Passive

Heat sinks
 Thermal floor planning
 Vias-Routing

Objectives of management

Component reliability

Heat spreading (data, com, memories...)

Component performance/efficiency

Noise reduction (imagers, detectors)

Component operation

« Heat as a resource »
 Non-volatile memories (PCM)
 Thermo-optical modulation

● Thermal interface resistance / conductance

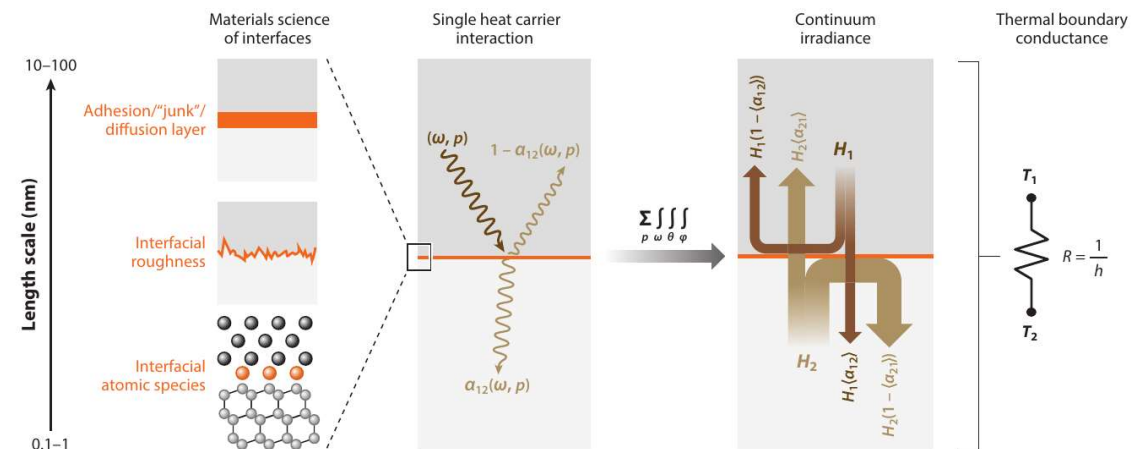
$$h_k = 1/R_k = \frac{\varphi}{\Delta T} [W \cdot m^{-2} \cdot K^{-1}]$$

Kapitza conductance technically refers to the conductance across an infinitesimally thin (atomically perfect and abrupt) surface or interface.

However, **Thermal Boundary Conductance** can refer to a more general, spatially broad interfacial region (ex :phonon scattering a few atomic layers away from the actual “interface” can dictate the reported h_k).

Main factors h_k for solid/solid

- Quality of the interface (roughness, oxyde)
- Strength of interatomic interactions at the interface
- Dispersion and density of states (DOS) for energy carriers
- Temperature
- Pressure



- Hopkins, P. E. (2013). “Thermal transport across solid interfaces with nanoscale imperfections: effects of roughness, disorder, dislocations, and bonding on thermal boundary conductance.” *International Scholarly Research Notices*, 2013.
- Monachon, C. et al. , *Annual Review of Materials Research*, **46**, 433-463.
- Maïté Blanck et al, *J. Appl. Phys.* **125**, 095302 (2019)
- A. Giri, and P. E. Hopkins, *Advanced Functional Materials*, **30**(8), 1903857 (2020)

● Thermal interface resistance / conductance

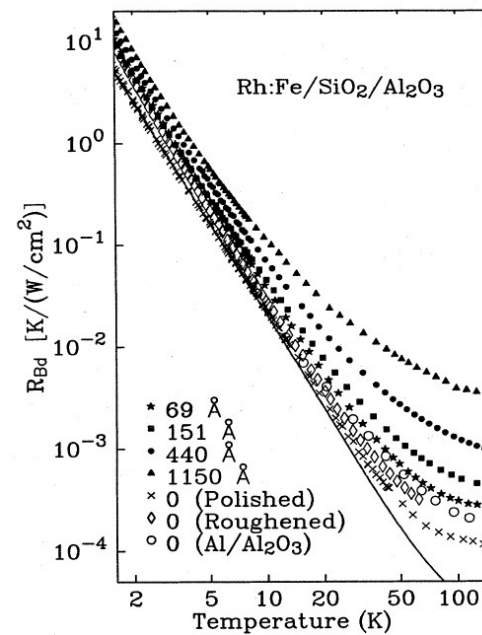
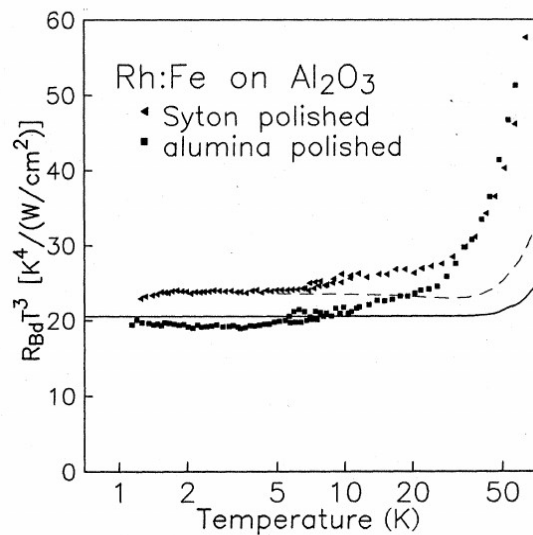
T^3 dependence at low T

« Thermal resistance at interfaces »

E. T. Swartz and R. O. Pohl, *Appl. Phys. Lett.* **51**, 2200 (1987)

« Thermal boundary resistance »

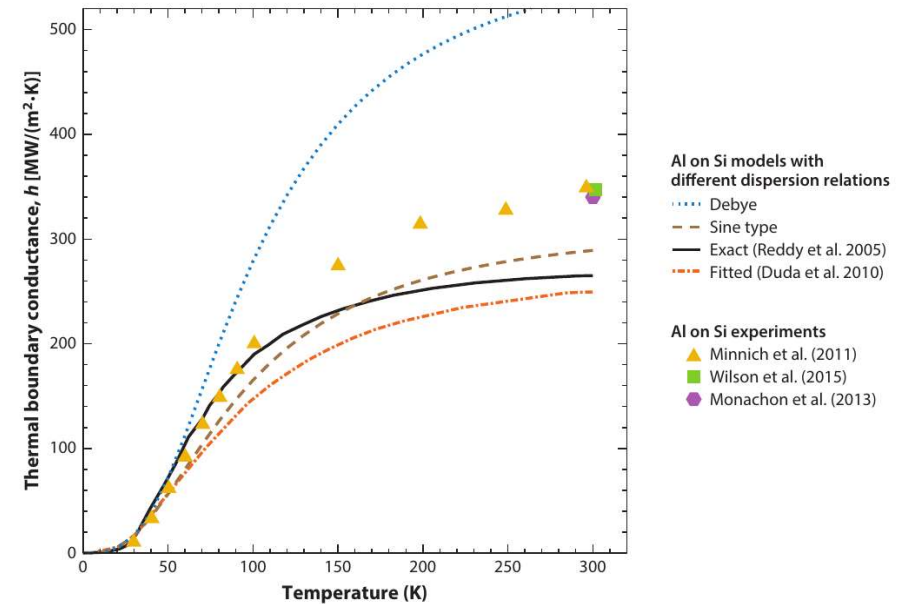
E. T. Swartz and R. O. Pohl, *Rev. Mod. Phys.* **61**, 605 (1989)



Diffuse Mismatch model

C. Monachon, et al. ,

Annual Review of Materials Research, **46**, 433-463.

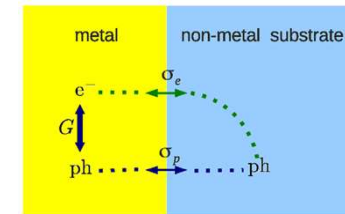


Thermal Management for IC

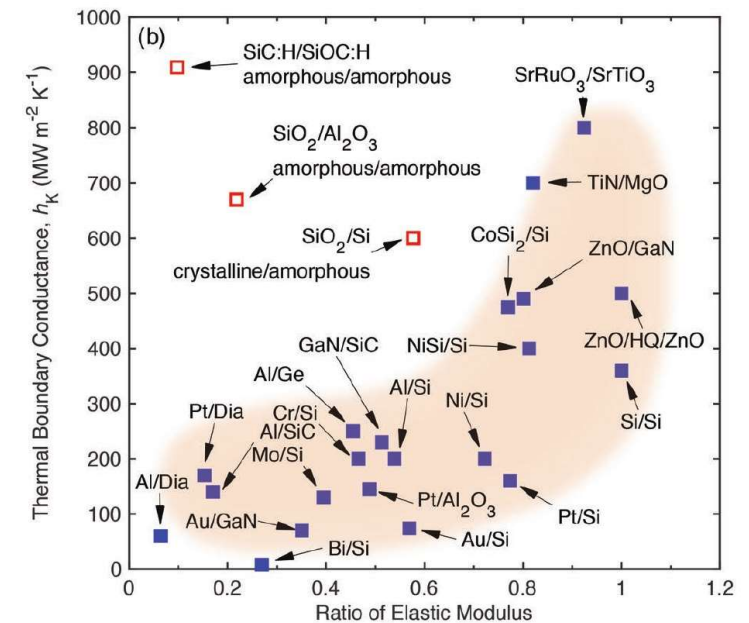
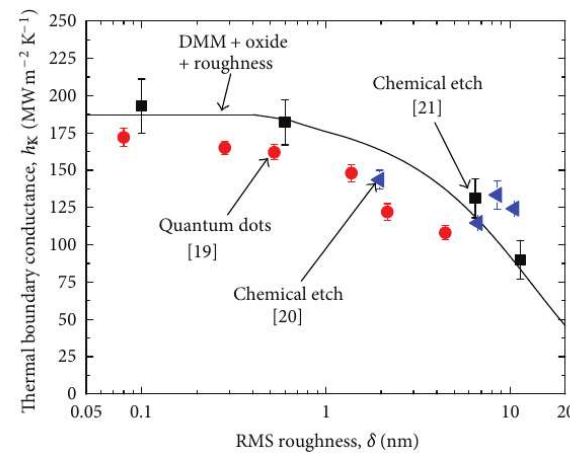
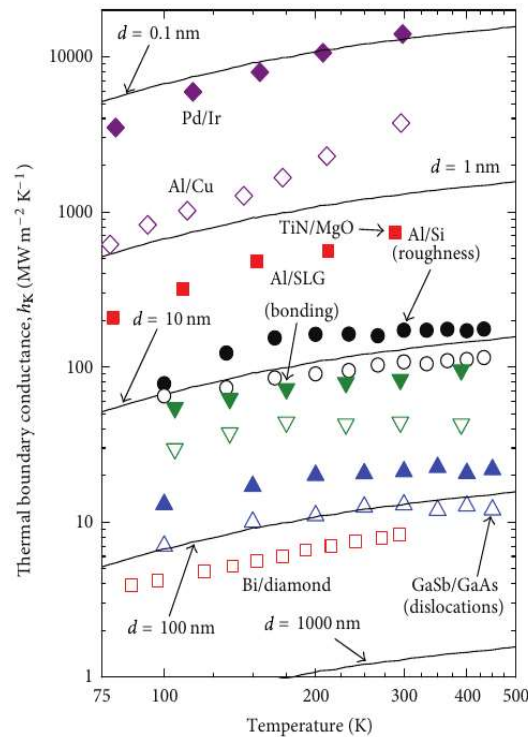
N. Horny

● Thermal interface resistance / conductance

- metal-metal : TBC is dominated by electron transport
- metal-nonmetal : TBC is dominated by phonon transport
- Effect of roughness
- Effects of Lattice Dislocations



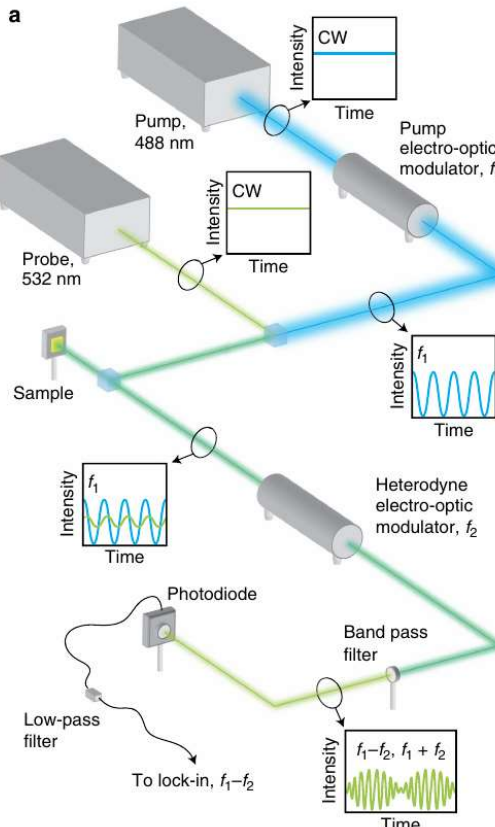
J Lombard, F Detcherry and S Merabia, *J. Phys.: Condens. Matter* 27 (2015).



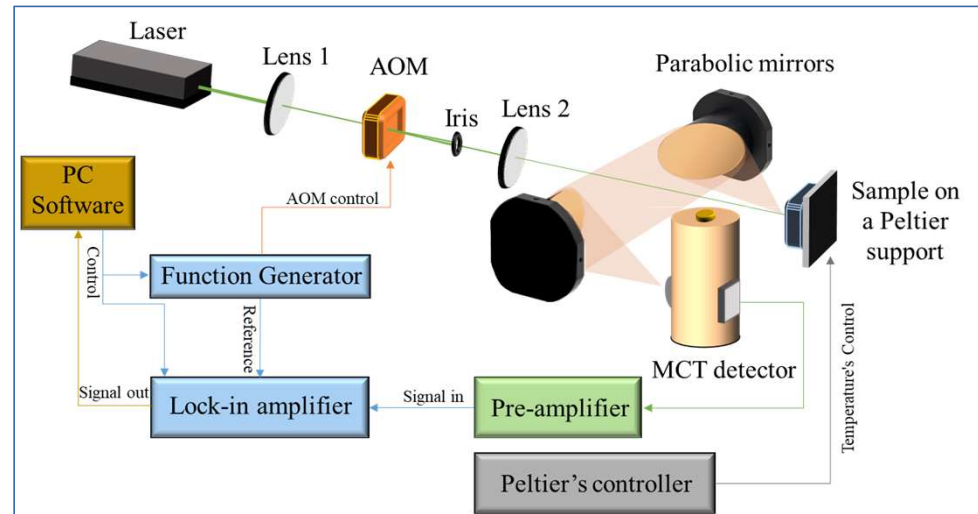
Hopkins, P. E. (2013). "Thermal transport across solid interfaces with nanoscale imperfections: effects of roughness, disorder, dislocations, and bonding on thermal boundary conductance." *International Scholarly Research Notices*, 2013.

A. Giri, and P. E. Hopkins, *Advanced Functional Materials*, 30(8), 1903857 (2020)

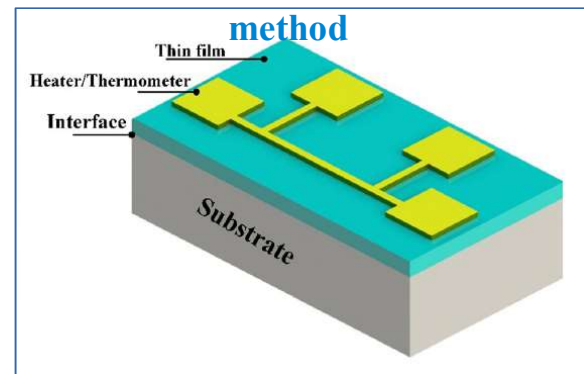
Time or frequency domain



Time or frequency domain Photothermal Radiometry



3ω

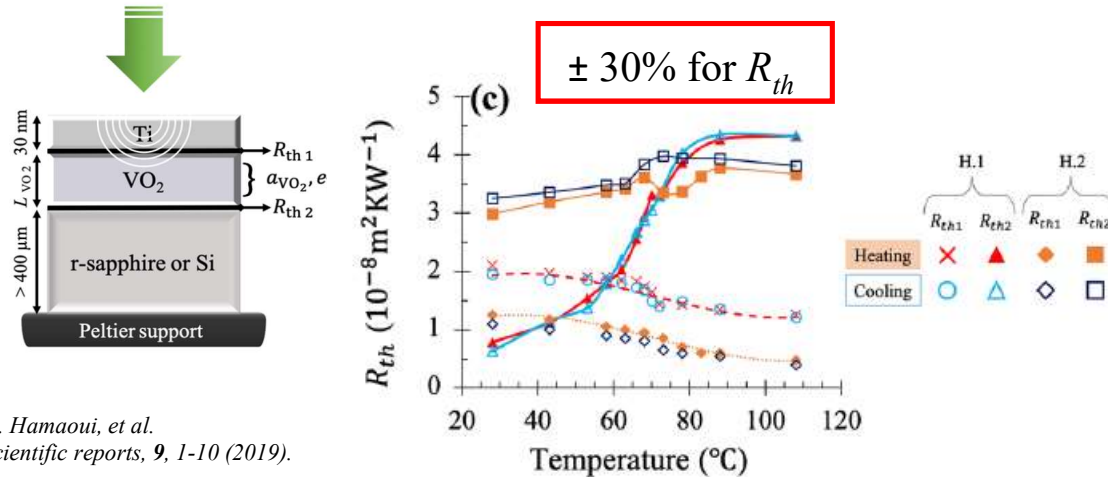


Thermal Management for IC

N. Horny

● Applications ● Phase Change Materials devices

Thermophysical characterisation of VO₂ thin films hysteresis



G. Hamaoui, et al.
Scientific reports, 9, 1-10 (2019).

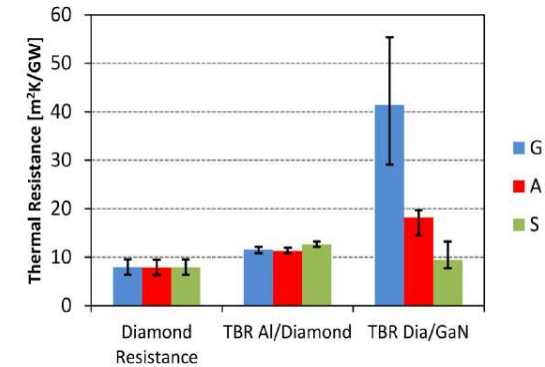
Low Thermal Boundary Resistance Interfaces for GaN-on-Diamond Devices

Al:80 nm	Al:80 nm	Al:80 nm
Diamond:1 μm	Diamond:1 μm	Diamond:1 μm
None	5nm AlN	5nm SiN
GaN: 500 nm	GaN: 500 nm	GaN: 500 nm
AlN Nucleation: 20 nm	AlN Nucleation: 20 nm	AlN Nucleation: 20 nm
SiC:500 μm	SiC:500 μm	SiC:500 μm

None: Sample "G"

AlN: Sample "A"

SiNx: Sample "S"



Yates et al., ACS Appl. Mater. Interfaces 2018, 10, 24302–24309 (2018)

Electronic contribution in heat transfer at metal-semiconductor and metal silicide-semiconductor interfaces

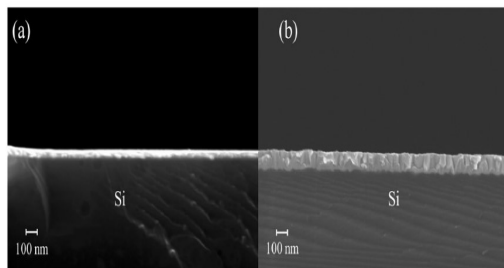
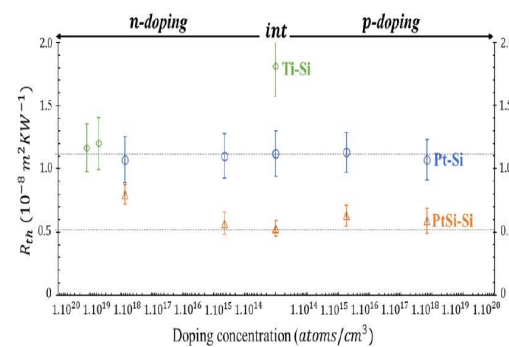


Figure 3. Example of a SEM images for the S3 samples: (a) unannealed Pt-Si and (b) annealed PtSi-Si samples.

G. Hamaoui et al. Scientific reports, 8, 1-9 (2018).

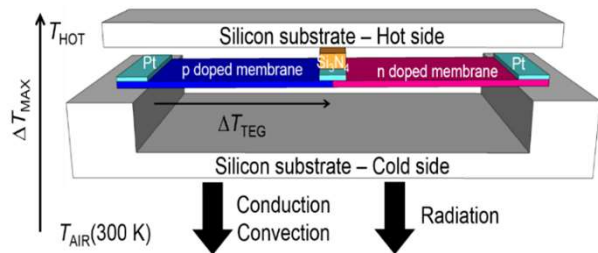


Thermal Management for IC

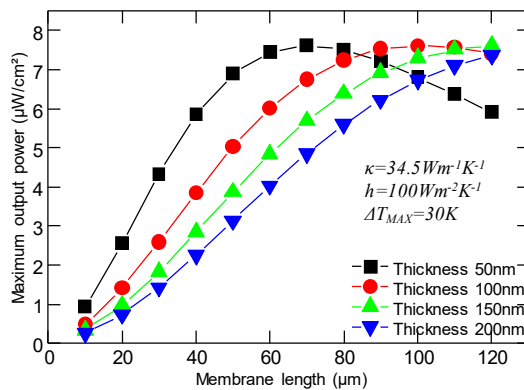
J.-F. Robillard

Applications • Thermoelectric Energy harvesting

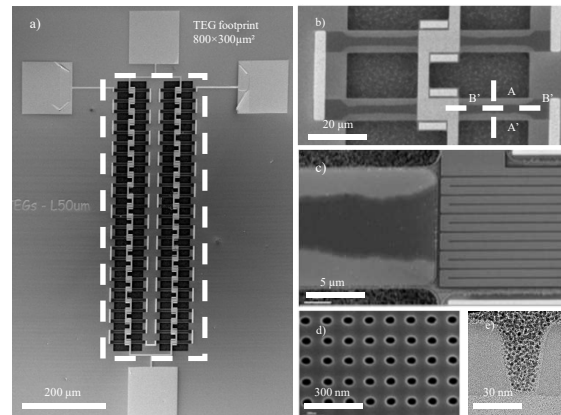
Attempts to integrate membrane-like or NW TE Converters lead to new thermal management issues.
Mainly related to the vertical to horizontal heat flux redirection
And air exchange.



Device optimization

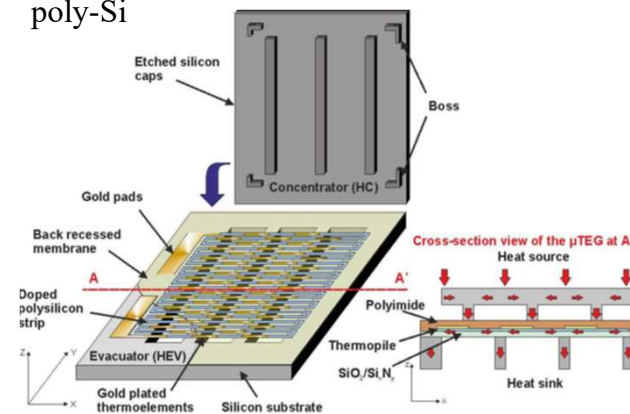


c-Si Membranes



M. Haras et al. *IEEE Electron Device Letters*, 37, 1358 (2016)
T. M. Bah et al. (in prep.)

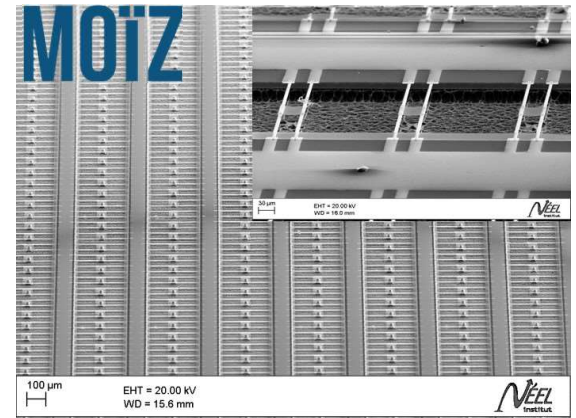
poly-Si



K. Ziouche et al. *Journal Of Microelectromechanical Systems*, 26, 45 (2017)

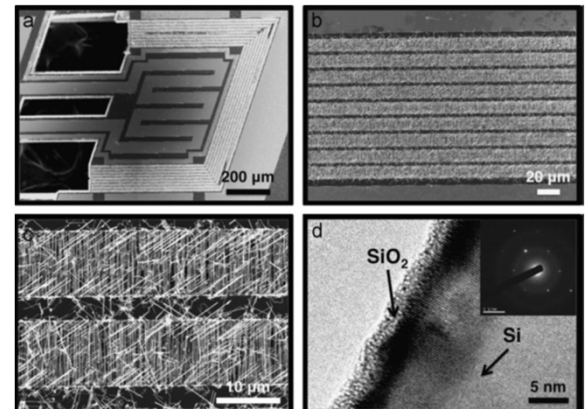
Bi₂Te₃

Air flow



D. Tainoff et al. *Nano Energy* 57 804–810 (2019)

c-Si NW



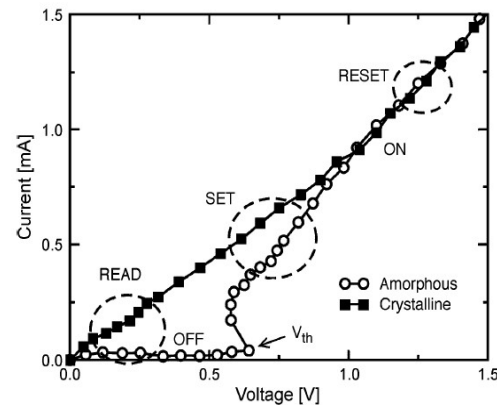
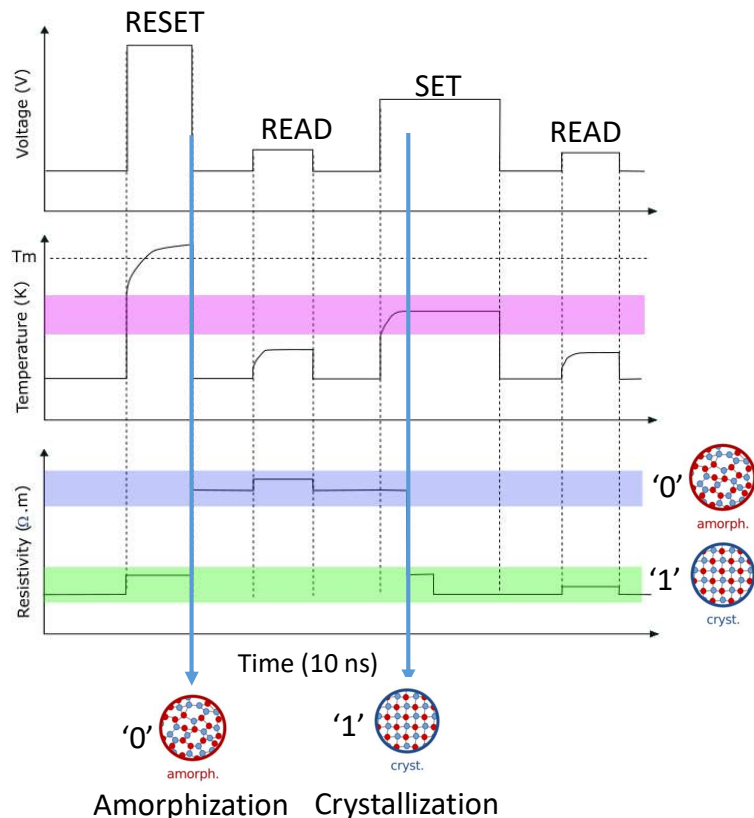
D. Davilà et al. *Nano Energy* 1, 812 (2012)

Thermal Management for IC

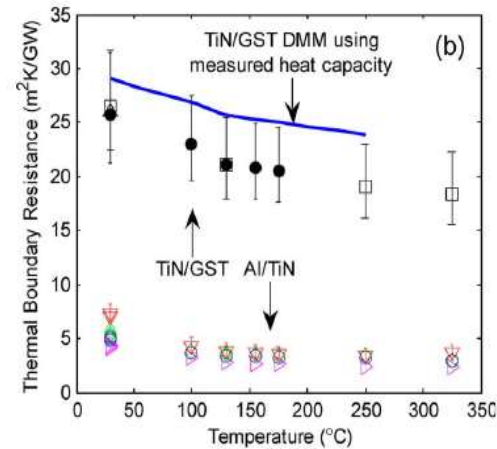
J.-F. Robillard
R. Simola

Applications • Phase Change Materials devices

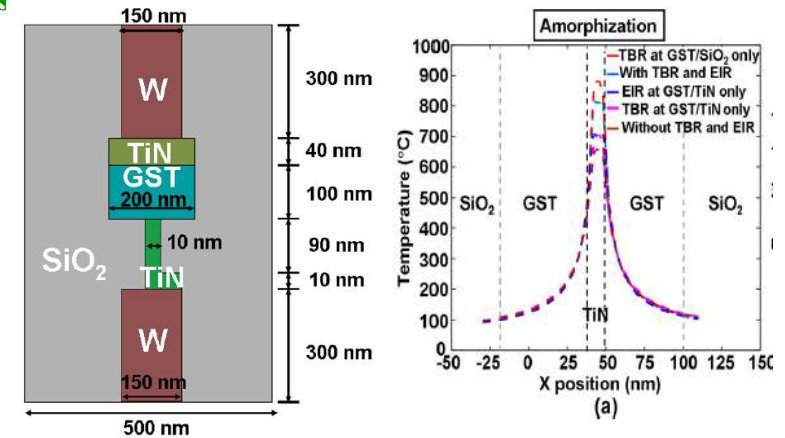
- Transition between amorphous and crystalline phase
- Phase transition – current induced Joule heating
- Information stored in the resistance of the alloy



A. Pirovano et al IEEE
Trans. Electron Devices, **51**, 452 (2004).

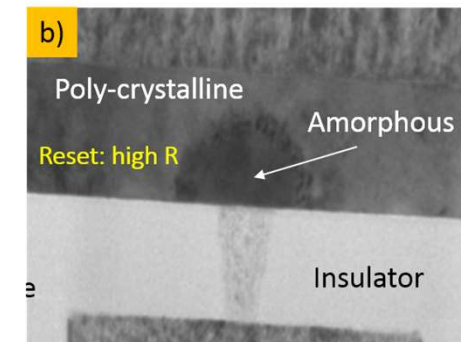


John P. Reifenberg, et al.
IEEE Electron Device Letters, **31**, NO. 1, (2010)



J. Wen et al IEEE Transactions on Electron Devices, **67** (2020)

Typical thicknesses of μ elec layers have a thermal resistance equivalent to TBR. TBR can be a major contribution to the total thermal resistance.



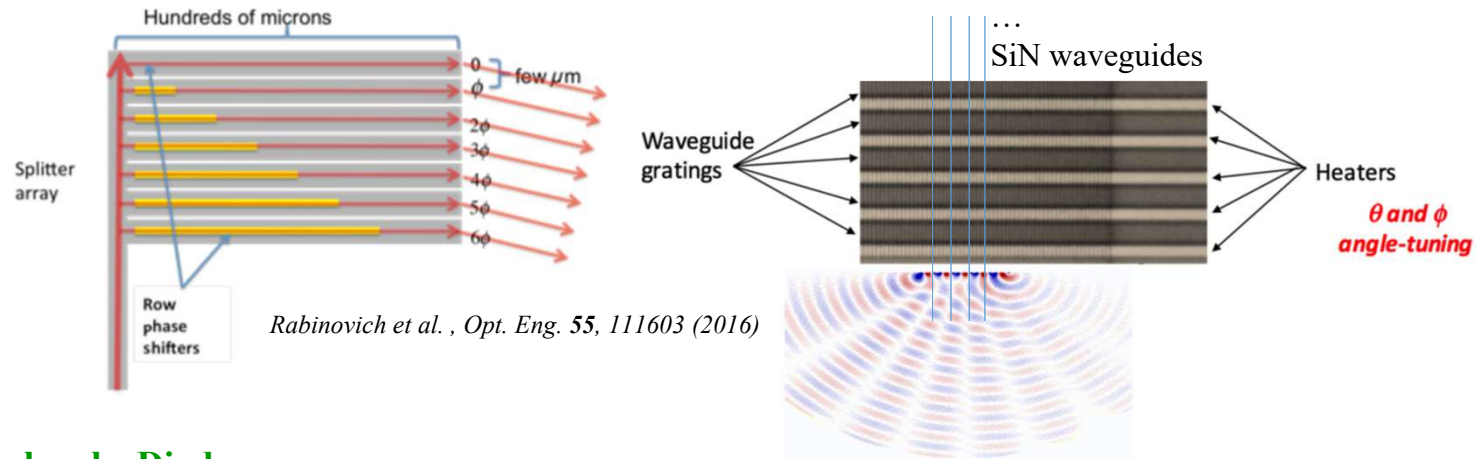
IBM Research / Memory Technologies

Thermal Management for IC

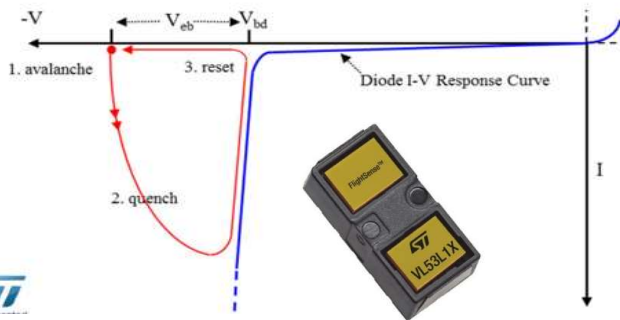
J.-F. Robillard
S. Monfray

● Applications ● LIDAR: Beam steering with thermo-optical waveguides

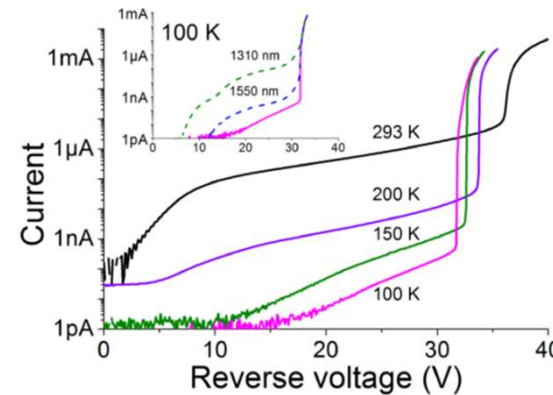
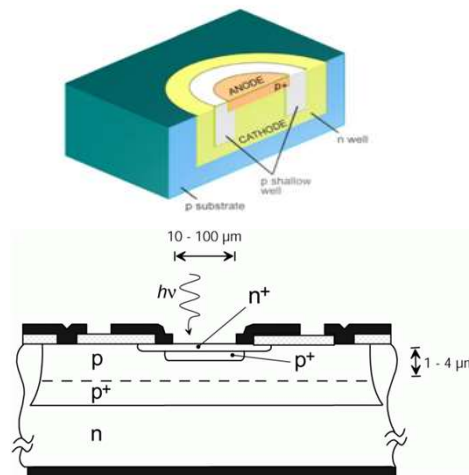
- For IR (905 nm)
- SiN waveguides
- Thermo-optical modulation
- Challenge=go to high frequencies (10-50kHz)
- Need for thermal optimization



● Detection and imaging : Single Photon Avalanche Diodes



Si 905 nm
Ge 1300 nm



- Dark Count Rate
- Noise Eq. Power

Can be highly improved through local cooling

R. E. Warbuton et al., Trans. on Electron devices, 60, 3807 (2013)

Thermal Management for IC

J. Maire

● **Techniques** ● **Passive: Thermal interface materials**

TIMs for 5G/AI/Semiconductors

Electrically conductive adhesives - alternative to solders (electronic packaging)

Elastomer socket powder – semiconductor testing

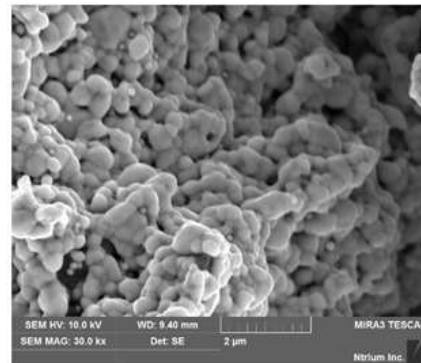
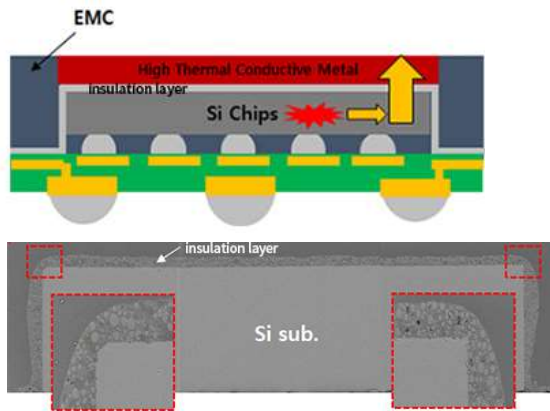
Conductive powder - touch screen panels



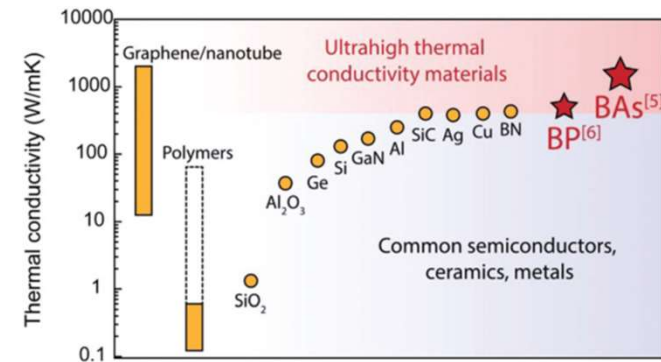
» Ni + Ag + Au

High thermal ceramic paste for spray – electrical insulator / spray

High Thermal Ag Sintering Paste – high thermal conductivity



Ultrahigh phonon conductivity materials

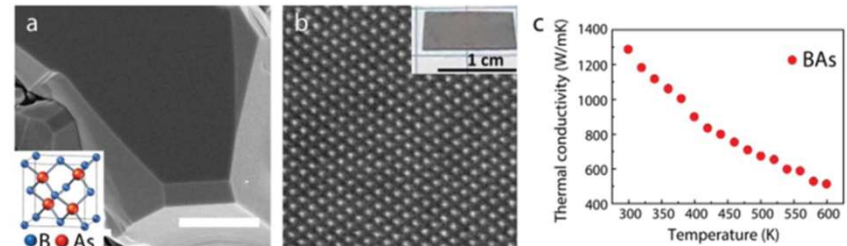


Primarily Synthetic diamond, BN, SiC, Ag, Al, and Cu

**Coefficient of thermal expansion
should match the heat source**

acoustic phonon bunching
large acoustic-optical gaps

e.g., BP, BAs



Thermal Management for IC

J. Maire

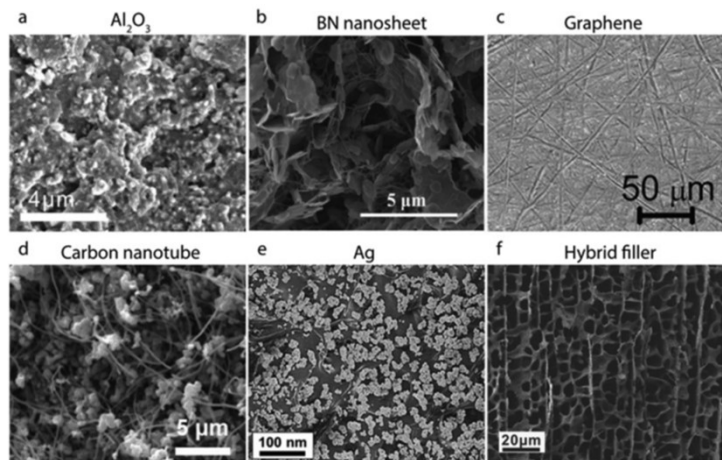
Techniques

Passive: Thermal interface materials

2D Materials for thermal management

Fillers for Polymer-Based TIMs

- Ultrahigh thermal conductivity of graphene (semi-metal)
- high conductivity of h-BN (insulator)

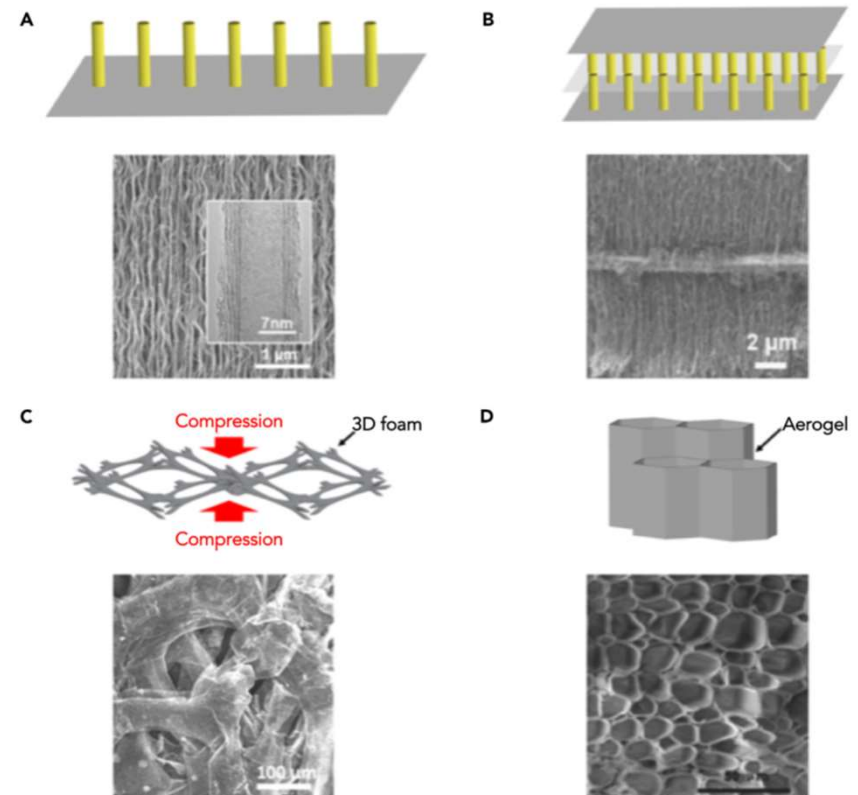


high κ with minimized filler loading

- graphene flakes with Ag particles
- h-BN flakes with SiC nanowires
- Ag flakes with CNTs

Direct Use for Thermal Management

2D Materials and 3D assemblies



- 3D-Interconnected Graphene and H-BN Macroforms Graphene and h-BN Thin Films for Heat Spreaders
- Graphene Fibers for Thermal Management

Thermal Management for IC

● Challenges and perspectives

● Challenges

- Heterogeneity : increased functional density leads to more materials and complex structures
- Mechanical flexibility : can lead to extra thermal resistance due to transfer bonding
- Metrology : TBR in realistic devices stacks
- Modeling : Taking into account non-Fourier conduction in complex structures
- Introduction of nanostructures in devices (NW, membranes) : Leads to new challenges in thermal design
- Paradoxically, high thermal conductivity nanostructures (carbon NW, graphene) can lead to degraded thermal management

● Perspectives

- Very high phonon conductivity materials
- Integrated Peltier cooling
- « Heat as a resource » devices (PCRam, PC Switches)

Atelier 4

Thermal Management

About this workshop:

- Very rich contents within the GDR and beyond
- We realized that some topics are not covered at all -> Please join !
- This is quite transversal topic and related to other Workshops.

Difficulties:

- Terminology and scope definition

The full presentation,
including Radiative Cooling and Thermotronics,
will be presented in next session, October.

Thanks to all contributors :

Younès Ezzahri
Jean-François Robillard
Philippe Ben-Abdallah
Jérémy Drévuillon
Nicolas Horny
Karl Joulain
Jérémy Maire
Stéphane Monfray
Elyes Nefzaoui
Stéphane Pailhès
Roberto Simola

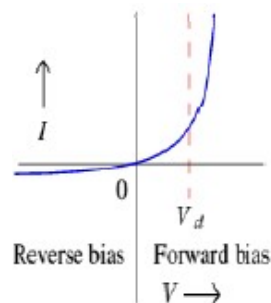
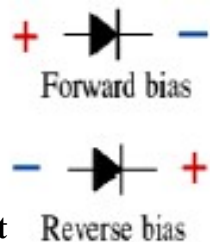
Thermotronics

P. Ben-Abdallah
Y. Ezzahri
K. Joulain

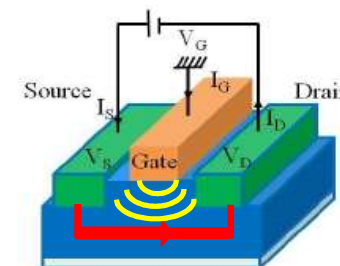
Historical breakthroughs in electronics

Diode

F. Braun
1874



J. Bardeen, W. Brattain,
W. Shockley
1947-1951



Transistor (FET)

- Electrical switching
- Modulation
- Current amplification

A variety of thermal analogues to the electronic components

N. A. Roberts and D. G. Walker, *IJTS*, **50**, 648 (2011).

"1936: First experimental observation of thermal rectification"

C. Starr, « The copper oxide rectifier », *Journal of Applied Physics*, **7**, 15-19 (1936).

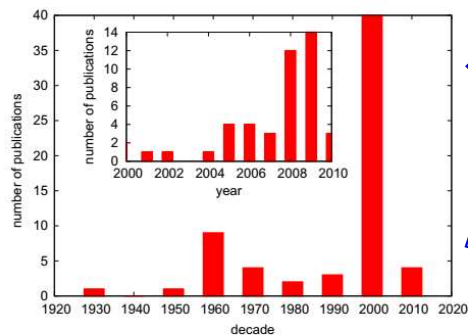


Fig. 1. Number of publications on thermal rectification per decade since 1936.

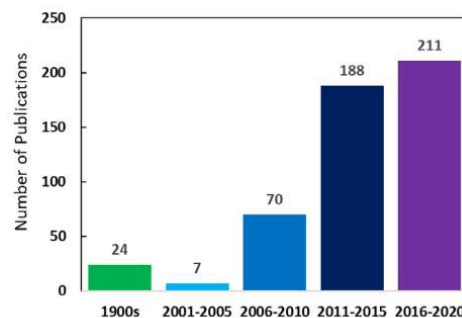
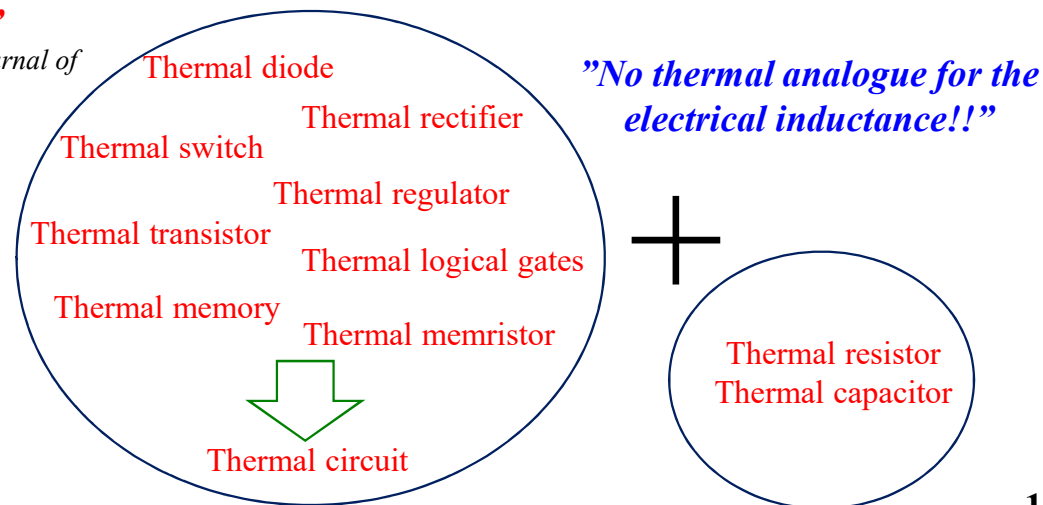


Fig. 2. Number of publications of thermal diode studies from the 1900s to present.

M. Y. Wong, C. Y. Tso, T. C. Ho and H. H. Lee, *IJHMT*, **164**, 120607 (2021).



Thermal rectifiers and thermal diodes

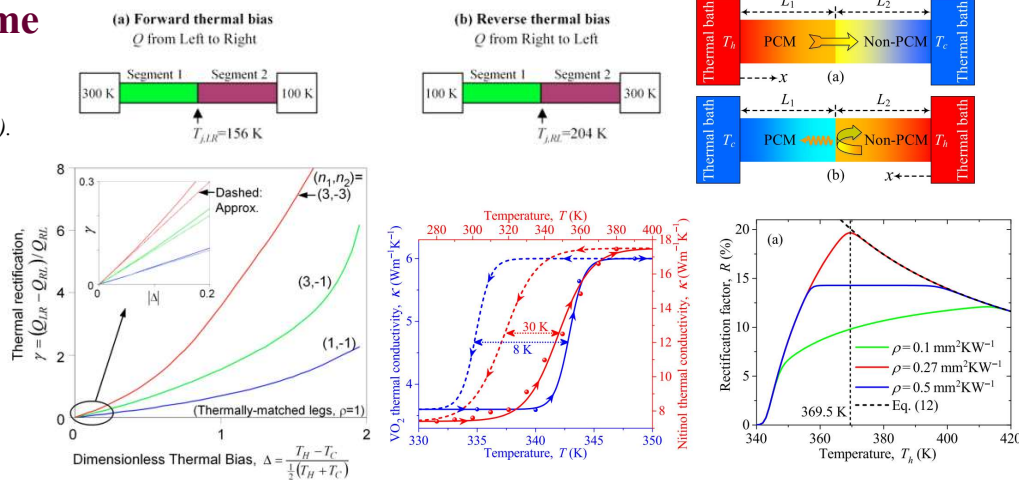
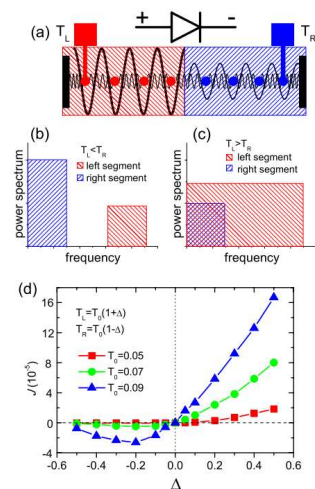
Different mechanisms

- **Conductive regime:** Asymmetric mismatch in phonon spectra (Nonlinear lattice coupled with harmonic spring) / Asymmetric Kapitza resistance / Asymmetric temperature dependent thermal conductivity / Metal-insulator transition (hysteretic thermal behavior of Phase transition materials PTM) → **Phononics**.
- **Radiative regime:** Resonance modes and broadband (selective emitters, superconductors and PTM) → **Photonics**.
- **Convective regime** also.

Conductive regime

Theory

B. Li et al., PRL, 93, 184301 (2004).



C. Dames, JHT, 131, 061301 (2009).

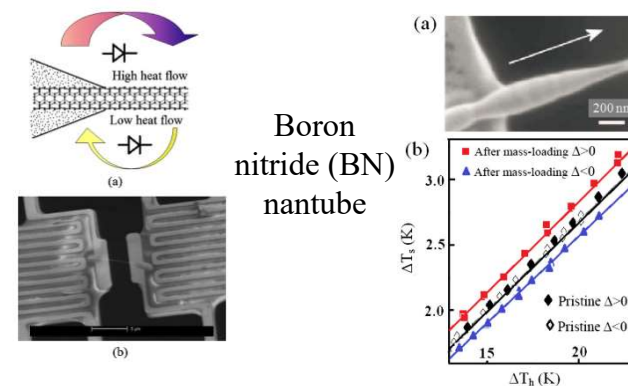
J. Ordonez-Miranda et al., JAP, 123, 085102 (2018).

Rectification factor

$$R = \frac{|\Phi_F - \Phi_R|}{\max\{\Phi_F, \Phi_R\}}, \frac{|\Phi_F - \Phi_R|}{\Phi_{F,R}}, \frac{|\Phi_F - \Phi_R|}{\Phi_F + \Phi_R}, \frac{\Phi_F}{\Phi_R}$$

Experiment

C. W. Chang et al., Science, 314, 1121 (2006).



Boron
nitride (BN)
nanotube

Limitations:

- Kapitza resistance
- Speed of phonons
- Phonon-phonon interactions with strong temperature gradients

Thermotronics

P. Ben-Abdallah
Y. Ezzahri
K. Joulain

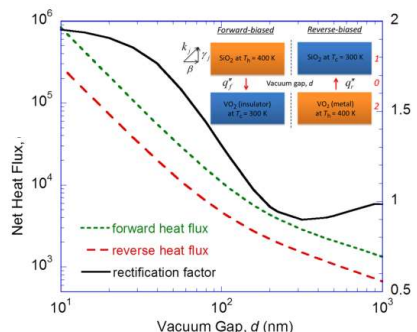
Thermal rectifiers and thermal diodes

Radiative regime

Theory

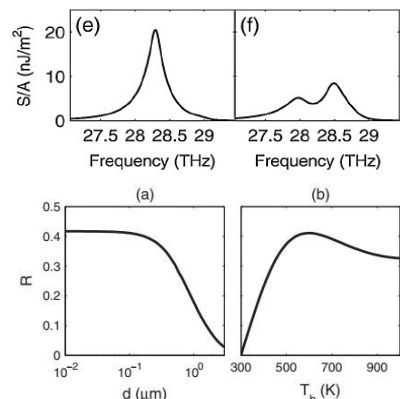
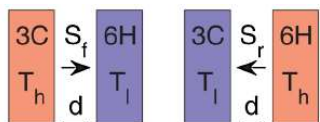
Thin film and bulk doped Si

Y. Yang et al., APL, 103, 163101 (2013).

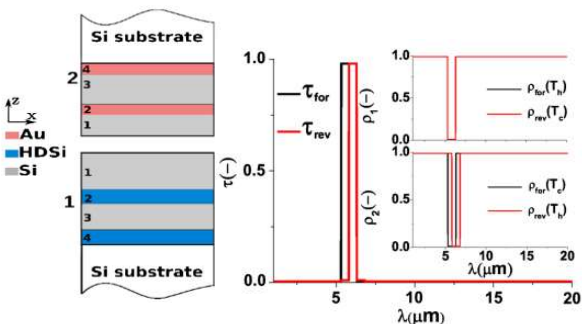


Near Field

Two slabs of SiC-3C and SiC-6H

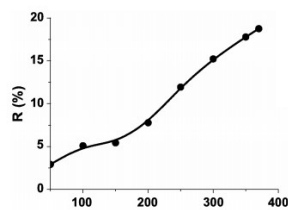


C. R. Otey et al., PRL, 104, 154301 (2010).



E. Nefzaoui et al., AO, 53, 3479 (2014).

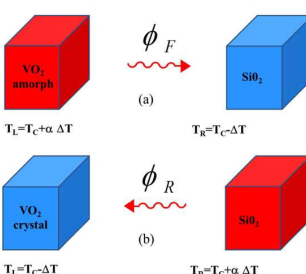
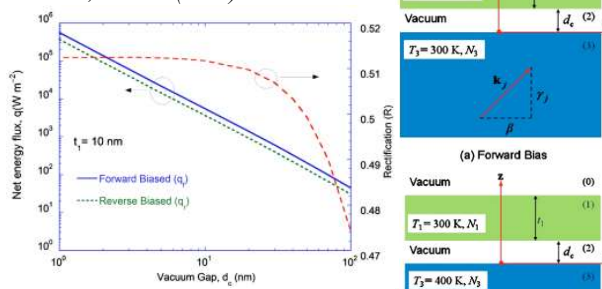
$$R = \frac{|\Phi_F - \Phi_R|}{\text{Max}\{\Phi_F, \Phi_R\}}$$



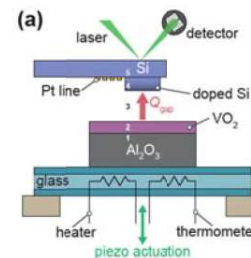
P. Ben-Abdallah and S. A. Biehs, APL, 103, 191907 (2013).

Far Field

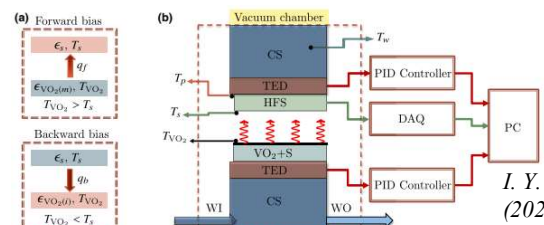
S. Basu and M Francoeur, APL, 98, 113106 (2011).



Near Field



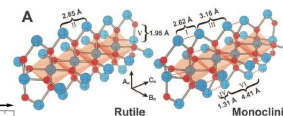
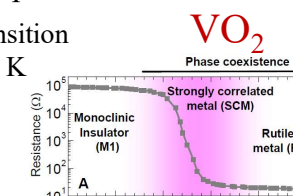
A. Fiorino et al., ACS Nano, 12, 5774 (2018).



Experiment

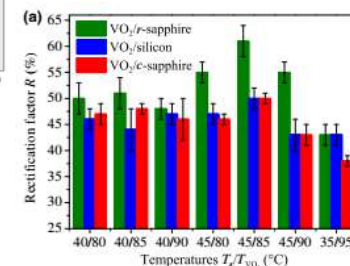
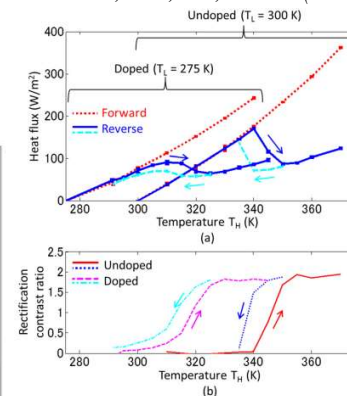
Using phase change (transition) materials or superconductors

Mott transition at 340 K



Far Field

K. Ito et al., APL, 105, 253503 (2014).



I. Y. Forero-Sandoval et al., PRA, 14, 034023 (2020).

Thermotronics

Thermal transistors

Conductive regime

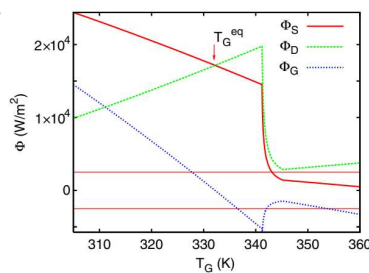
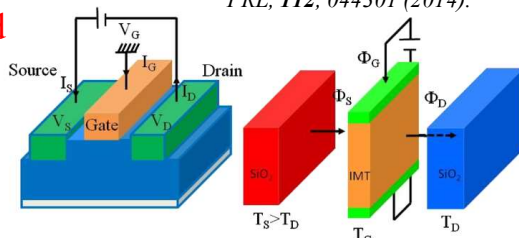
B. Li et al., *APL*, **88**, 143501 (2006).

"Thermal transistor effect ↔ negative differential thermal resistance"

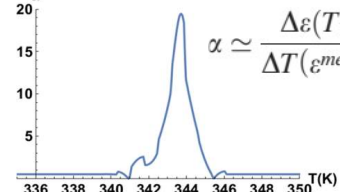
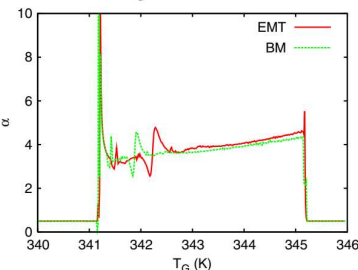
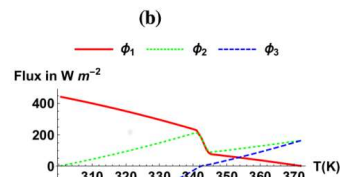
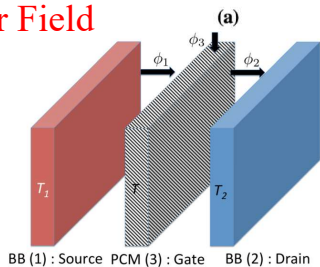
Radiative regime

P. Ben-Abdallah and S. A. Biehs, *PRL*, **112**, 044301 (2014).

Near Field



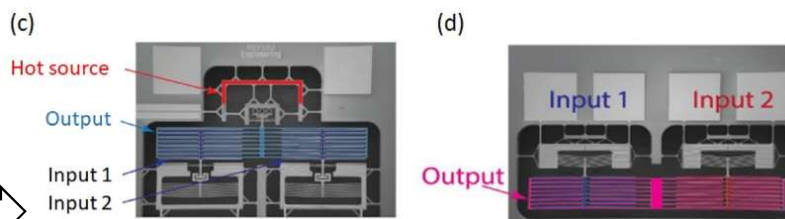
Far Field



Operating modes:

- 1-Thermal switch
- 2-Flux modulation
- 3-Flux amplification

SEM images of "AND" and "OR" NanoThermoMechanical gates



A. Hamed and S. Ndao, *Scientific Reports*, **10**, 2437 (2020)

Amplification factor

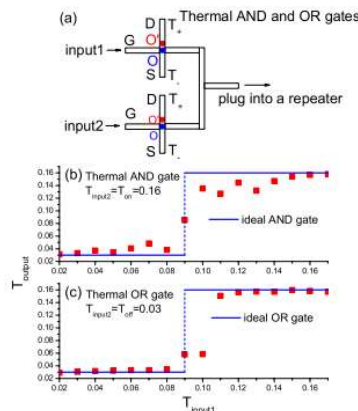
$$\alpha \equiv \left| \frac{\partial J_D}{\partial J_G} \right| = \left| \frac{R_S}{R_S + R_D} \right| > 1 \text{ SSS } R_S \text{ or } R_D < 0$$

N. Li, J. Ren, L. Wang, G. Zhang, P. Hänggi and B. Li, *Review of Modern Physics*, **84**, 1045 (2012).

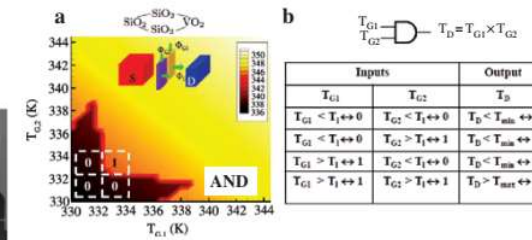
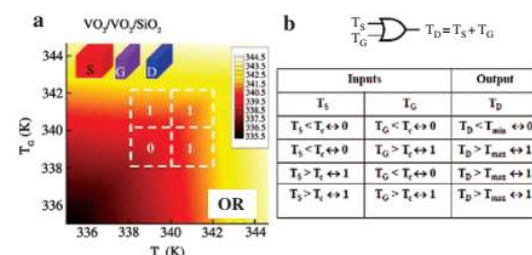
Thermal logical gates and memories

Conductive regime

L. Wang and B. Li, *PRL*, **99**, 177208 (2007).



Radiative regime



P. Ben-Abdallah and S. A. Biehs, *PRB*, **94**, 241401(R) (2016).

Thermotronics

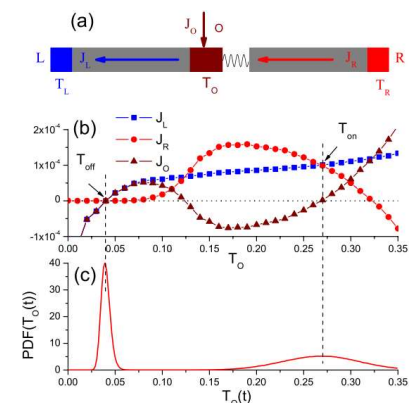
P. Ben-Abdallah
Y. Ezzahri
K. Joulain

Thermal logical gates and memories

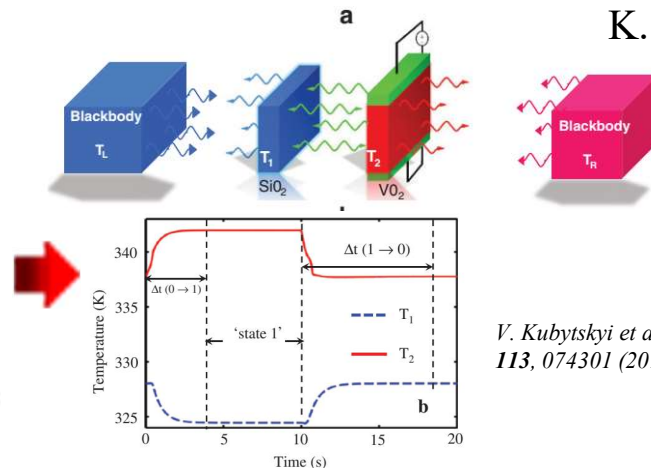
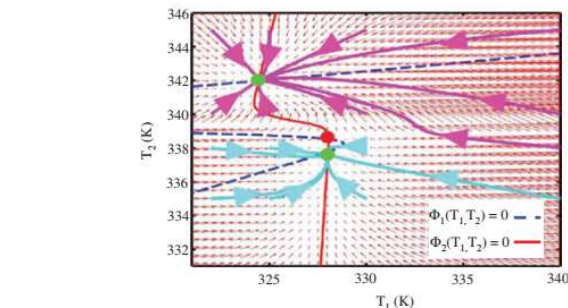
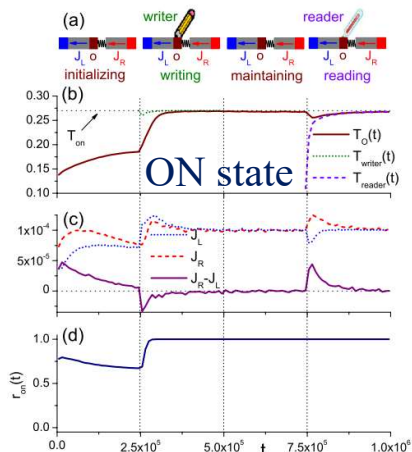
Conductive regime

Theory

Radiative regime



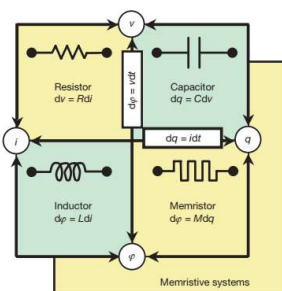
L. Wang and B. Li, PRL, 101, 267203 (2008).



V. Kubytskyi et al., PRL, 113, 074301 (2014).

Thermal memristor

Memristor = Memory resistor



Chua's Memristor

$$v = \mathcal{R}(w)i$$

$$\frac{dw}{dt} = i$$

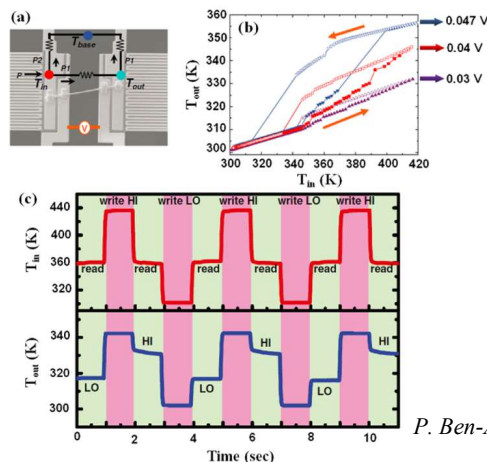
Memristive system

$$v = \mathcal{R}(w,i)i$$

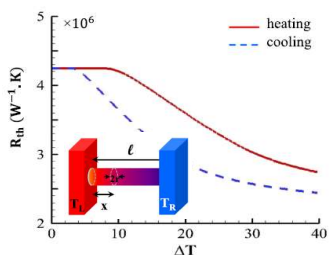
$$\frac{dw}{dt} = f(w,i)$$

- W is a state variable of the device.
- R is a generalized resistance.

Experiment

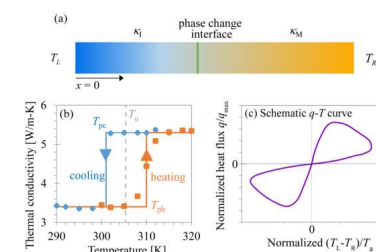


R. Xie et al., Adv. Funct. Mater., 21, 1602 (2011).



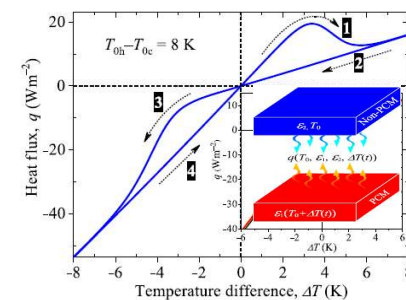
P. Ben-Abdallah, AIP Advances, 7, 065002 (2017).

Conductive regime



F. Yan et al., JAP, 125, 025109 (2019).

Radiative regime



State variable = volume fraction f

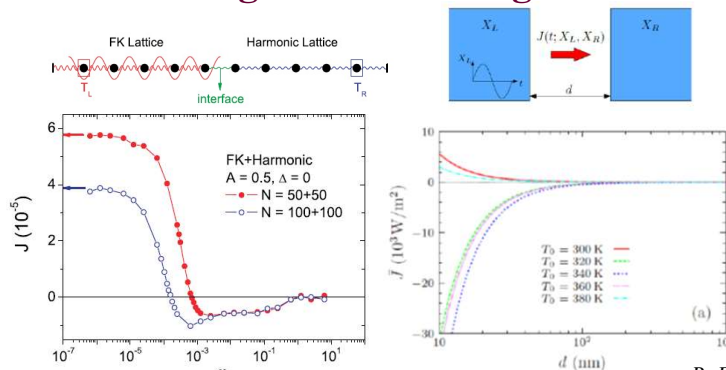
J. Ordonez-Miranda et al., PRL, 123, 025901 (2019).

Thermotronics

P. Ben-Abdallah
Y. Ezzahri
K. Joulain

Active control of heat flux

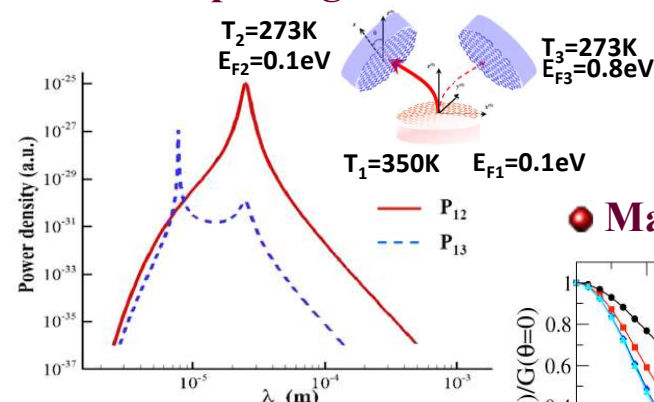
Shuttling and ratcheting



► Pumping heat against the thermal bias

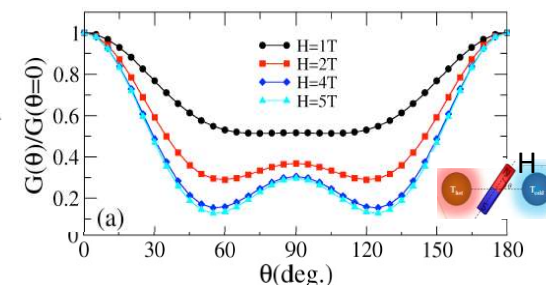
N. Li et al. *Phys. Rev. E* **80**, 011125 (2009); N.-B. Li et al. *Europhys. Lett.* **84**, 40009 (2008); I. Latella et al. *Phys. Rev. Lett.* **121**, 023903 (2018).

Heat splitting



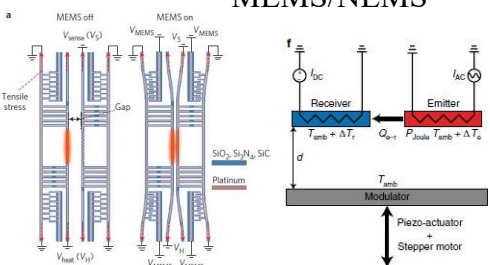
R. Ekeröth et al. *ACS Photonics*, **5**, 705, (2018).
I. Latella et al. *PRL* **118**, 173902 (2017).

Magnetic control



Mechanical control

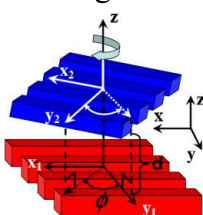
MEMS/NEMS



R. St. Gelais et al., *Nature Nanon* **11**, 515 (2016).

D. Thompson et al., *Nat. Nano*, **15**, 99 (2020).

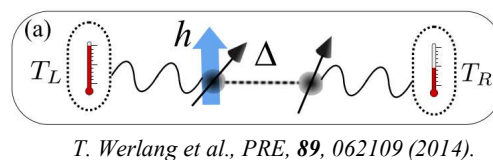
Gratings rotation



S.-A. Biehs et al. *APL*, **98**, 243102 (2011).

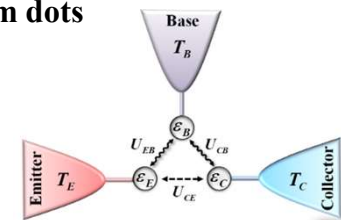
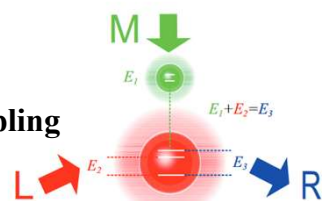
How about the quantum regime?

Thermal diode



T. Werlang et al., *PRE*, **89**, 062109 (2014).

Using Colomb-coupled quantum dots



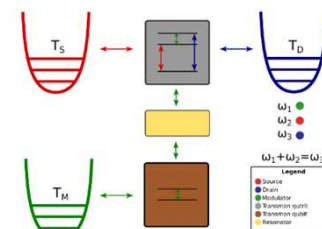
Y. Zhang et al., *EPL*, **122**, 17002 (2018).

Thermal transistor

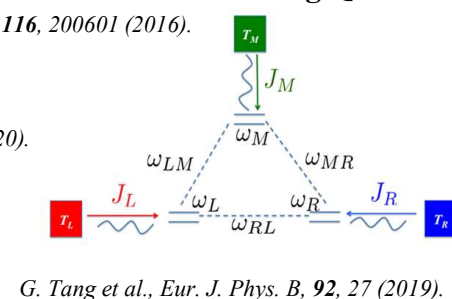
K. Joulain et al., *PRL*, **116**, 200601 (2016).

Using Superconductors

M. Majland et al., *PRB* **101**, 184510 (2020).



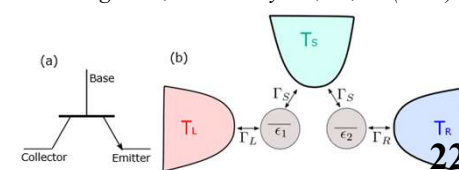
Using Qubits



G. Tang et al., *Eur. J. Phys. B*, **92**, 27 (2019).

Using Qubit-Qutrit coupling

B. Guo et al., *PRE*, **98**, 022118 (2018).



Challenges and perspectives

Challenges

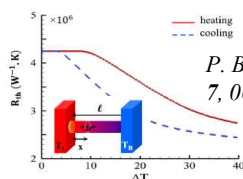
- The operating time scale in nanostructures ($\sim \mu\text{s}$ to s) is limited by the thermal inertia.



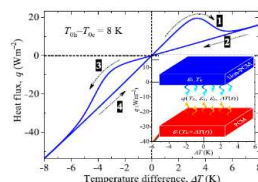
Perspectives

- Extension of the developed concepts to the conductive regime using Phase Transition Materials (e.g. VO_2).
- Exploring and deepening the analysis of the dynamical regime.
- Towards smart hybrid circuits and structures optimizing heat management and electronic operation ...
- Towards a full heat information treatment structure...

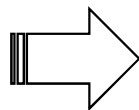
Memristive behavior



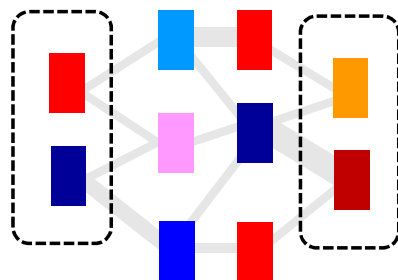
P. Ben-Abdallah, *AIP Advances* 7, 065002 (2017).



J. Ordonez-Miranda et al., *PRL* 123, 025901 (2019).



R. Yu, et al. *Nat Commun* 8, 2 (2017).

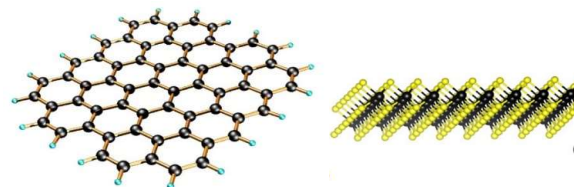


Input

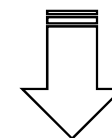
Output

Neuromorphic computing

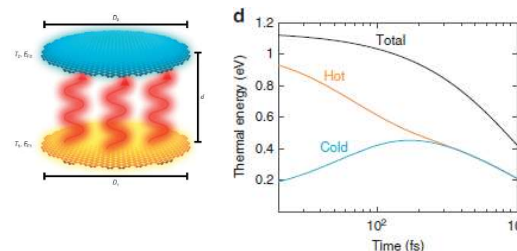
Two dimensional materials



- Transition metal dichalcogenide monolayers could allow to design thermal transistor operating at submicrosecond scale



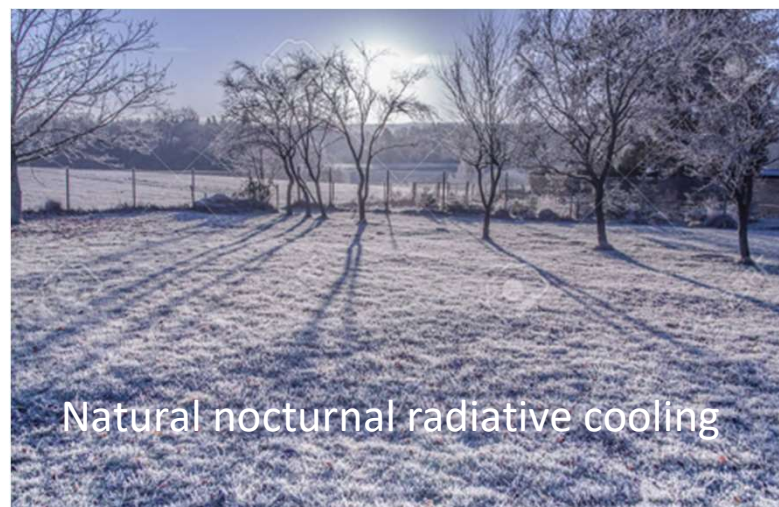
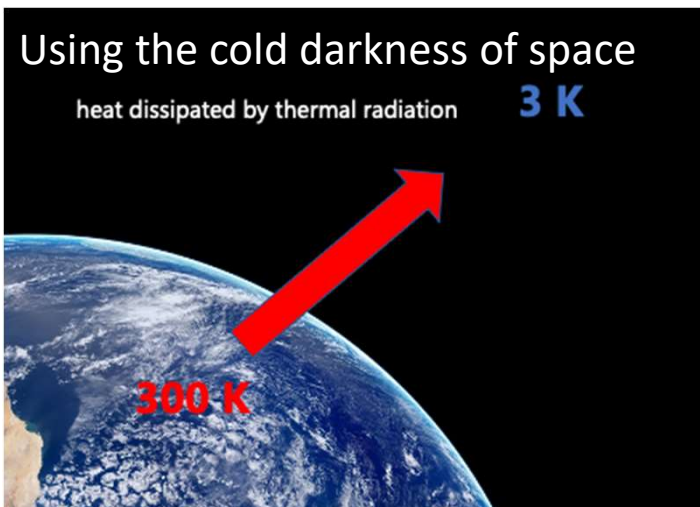
Systems far from equilibrium



- Electrons and phonons at different temperatures.
- Heat flux control at pico and subpicosecond scale...

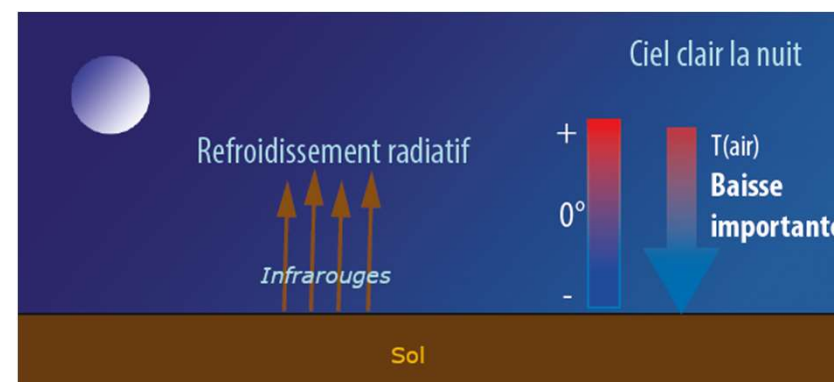
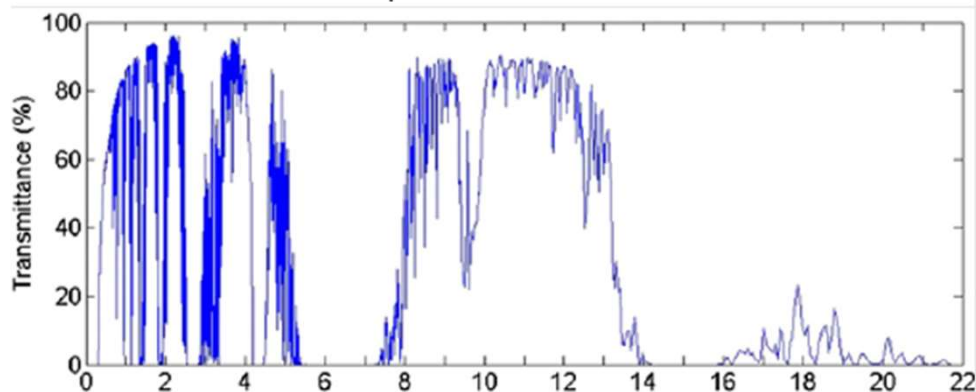
Radiative cooling

J. Drévillon



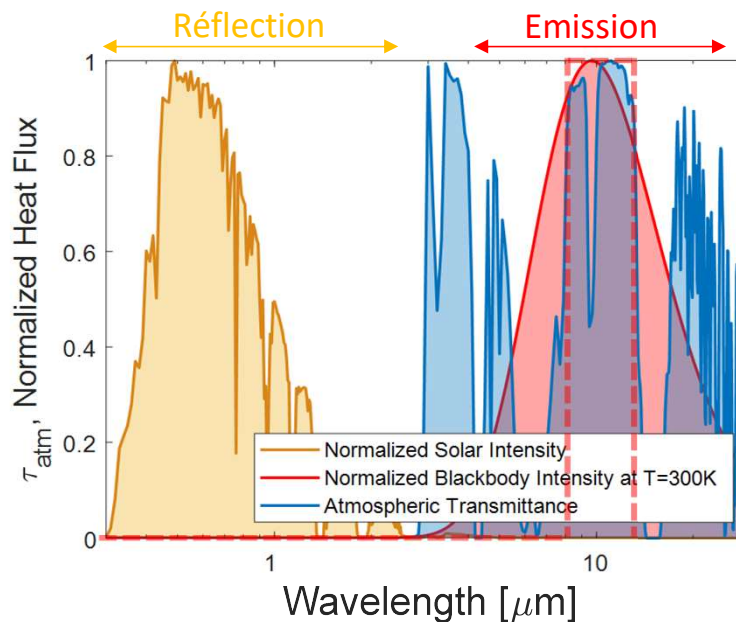
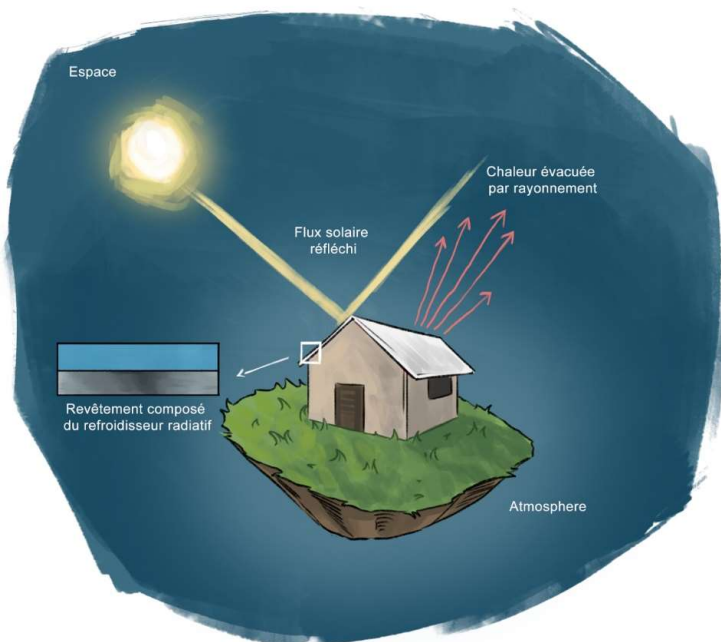
at night, objects and the ground cool by radiation, become colder than ambient

Atmospheric transmittance



Radiative cooling

J. Drévillon

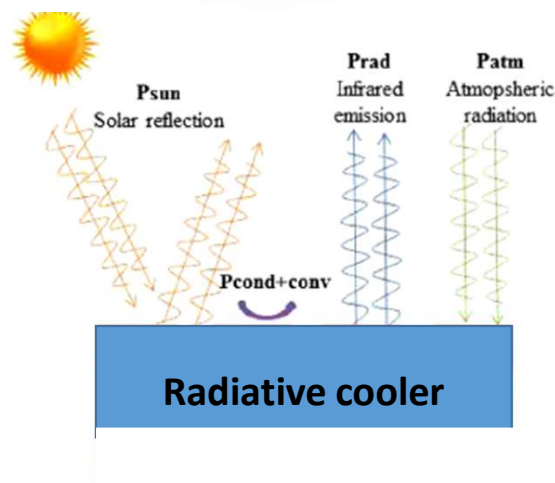


Cooling of the structure ($T = 300$ K) by direct heat transfer with space ($T = 3$ K).

No energy to provide for cooling

Design of coatings reflecting in the solar radiation spectrum and highly emitting in the IR

Control and optimization of radiative properties over a broad spectrum



Radiative cooling power

Power emitted by the structure

Absorbed incoming power from the sun

Power absorbed due to incident atmospheric radiation

Exchanged power due to conduction and convection

$$P_{cool}(T) = P_{rad}(T) - P_{atm}(T_{amb}) - P_{sun} - P_{cond+conv}$$

$$P_{rad}(T) = A \int d\Omega \cos \theta \int_0^\infty d\lambda I_{BB}(T, \lambda) \varepsilon(\lambda, \theta)$$

$$P_{atm}(T_{amb}) = A \int d\Omega \cos \theta \int_0^\infty d\lambda I_{BB}(T_{amb}, \lambda) \varepsilon(\lambda, \theta) \varepsilon_{atm}(\lambda, \theta)$$

$$P_{sun} = A \int_0^\infty d\lambda \varepsilon(\lambda, 0) I_{AM\,sw\,1.5}(\lambda)$$

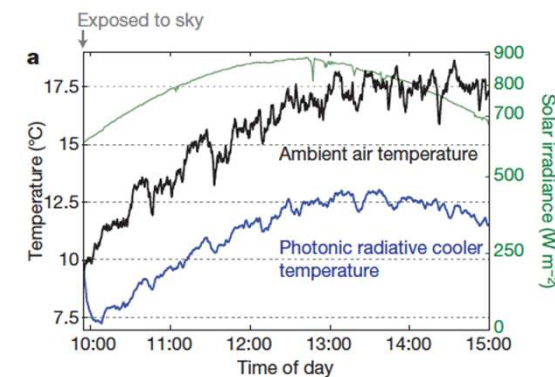
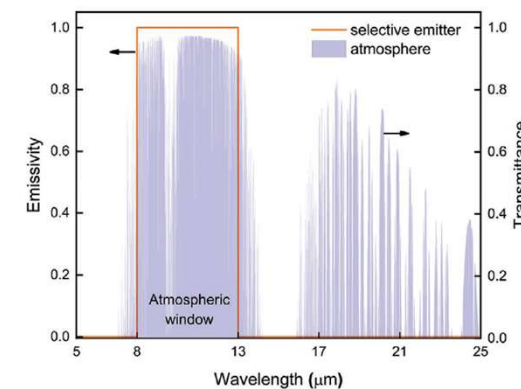
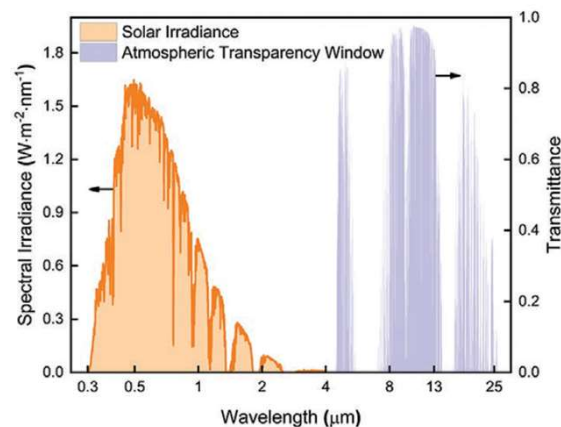
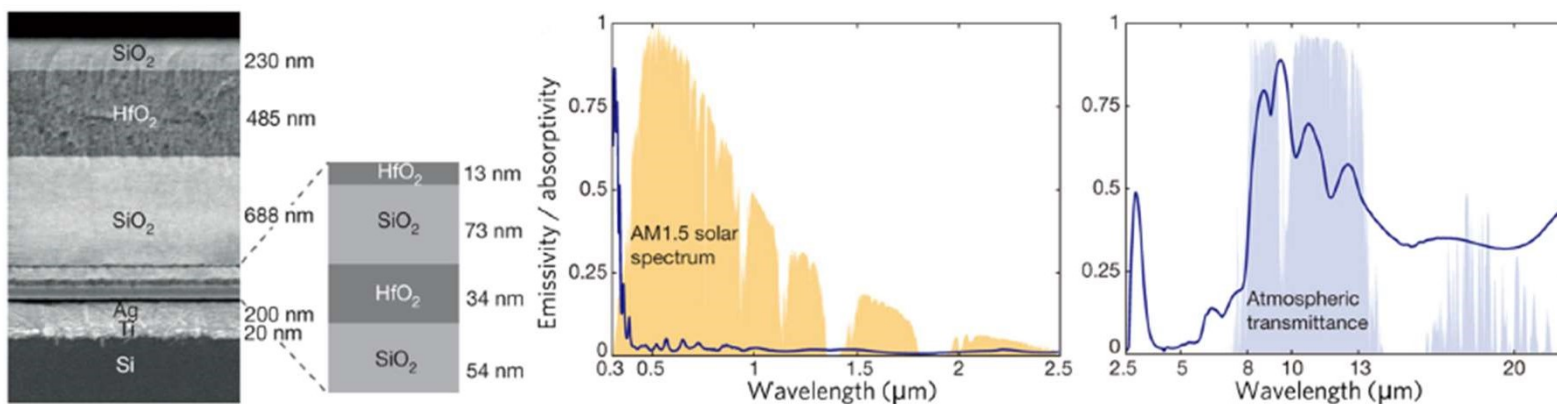
Radiative cooling

J. Drévillon

- How to minimize the absorption of solar radiation?
- How to optimize the emission of heat by radiation in the sky window?

Different approaches

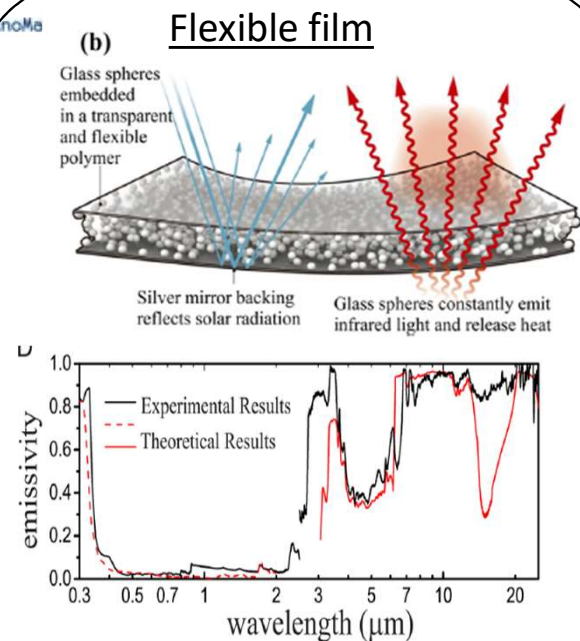
Nanophotonic approach: thin films stack



Always composed of two main parts aiming to

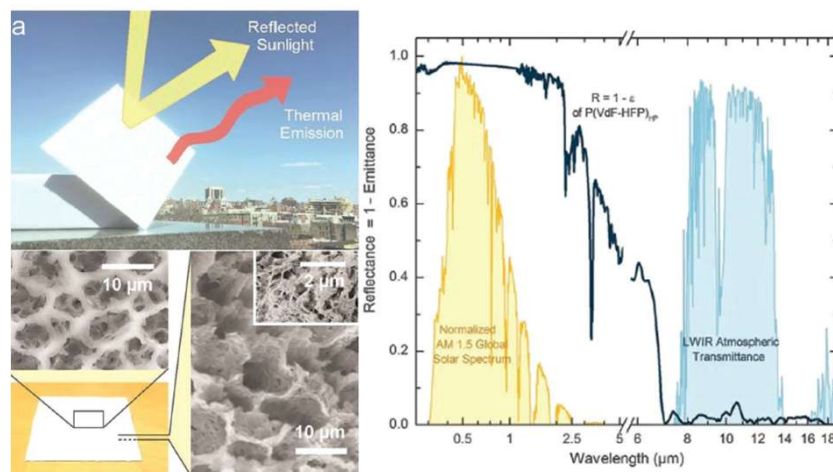
- increase the reflectivity of the structure in the short wavelength range (0,3-2,5 μm) - >solar spectrum
- Enhance the emissivity of the structure in the atmospheric window (8-13 μm)

AP. Raman et al., Nature, 515, 540 (2014).



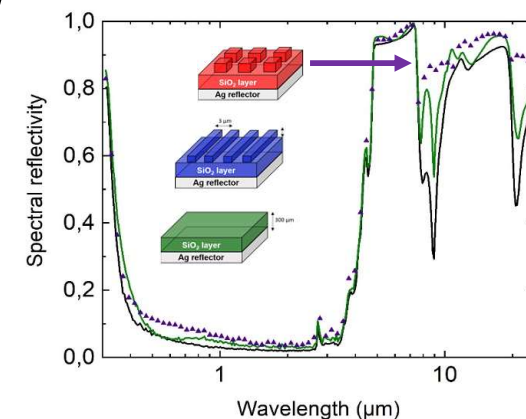
Zhai Y, *et al.*, *Science*, 2017

Nano/micro Porous Polymer



J. Mandal, *et al.*, *Science*, 2018

Patterned surface

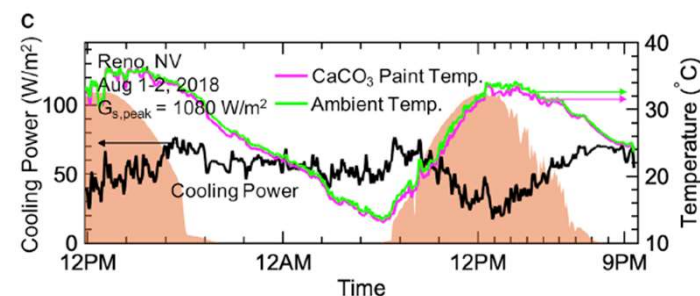
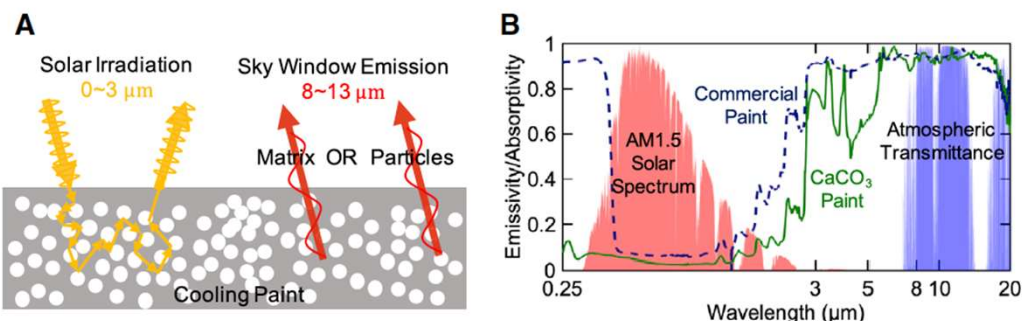


Etching of the surface grating by DRIE

Blandre E. *et al.*, *Optics Express*, 2020

Paints

Xiangyu Li, *et al.*, *Cell Reports Physical Science*, 2020

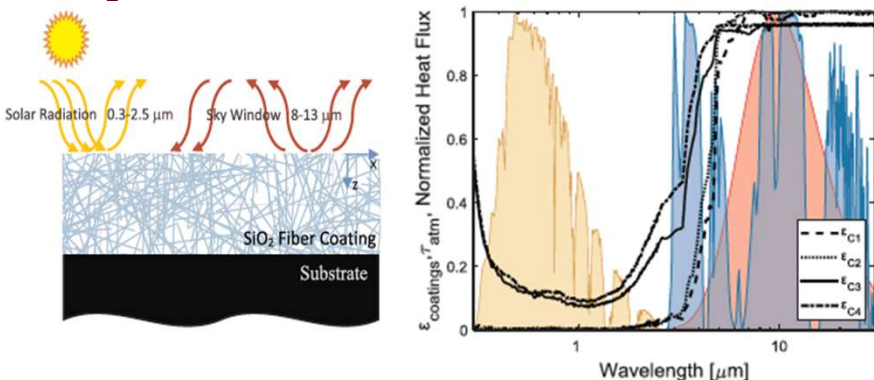


Radiative cooling

J. Drévilion
E. Nefzaoui

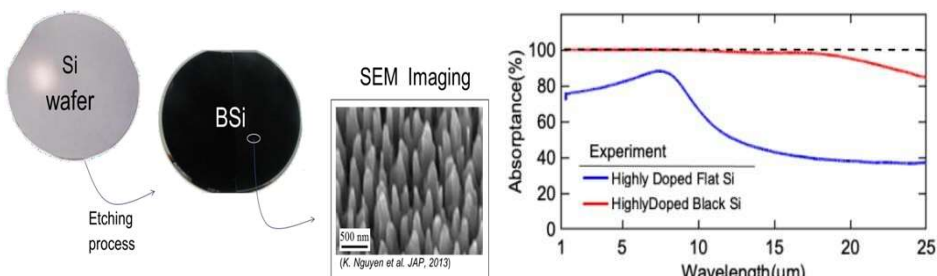
Different approaches

SiO₂ nanofibers

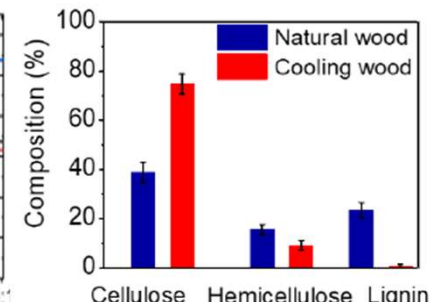
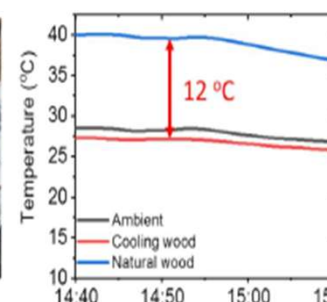
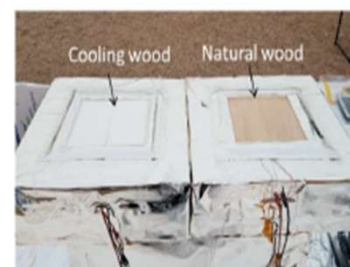


R. Yalçın *et al.*, Solar Energy Materials and Solar Cells, 2020

Black silicon (Bsi)

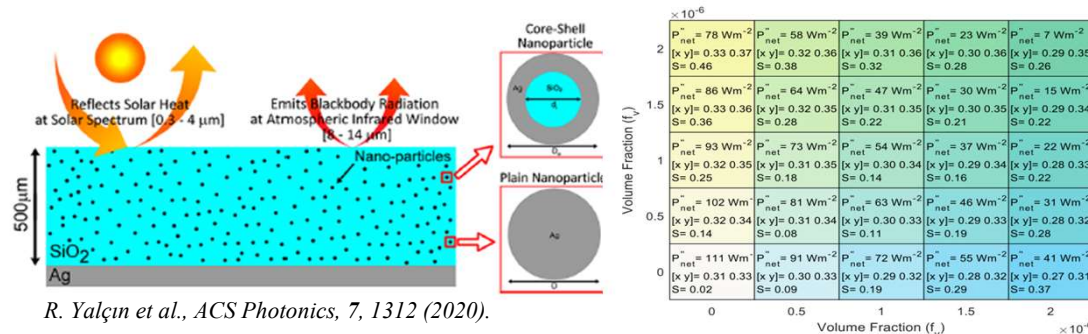


Delignified wood

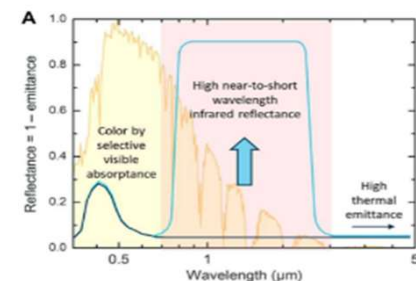
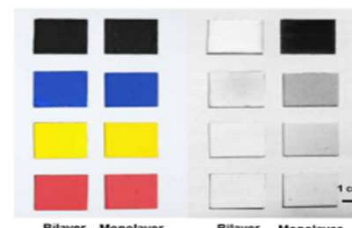


T. Li *et al.*, Science, 364, 6442 (2019).

Colored PDRC



R. Yalçın *et al.*, ACS Photonics, 7, 1312 (2020).



Y. Chen *et al.*, Science Advances, 6, 1 (2020).

Radiative cooling

J. Drévillon
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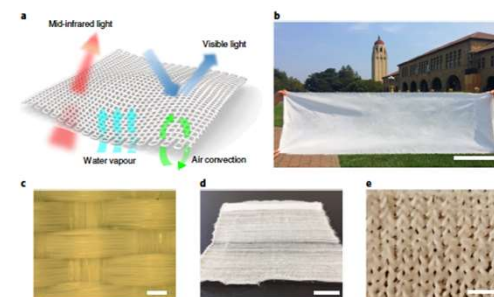
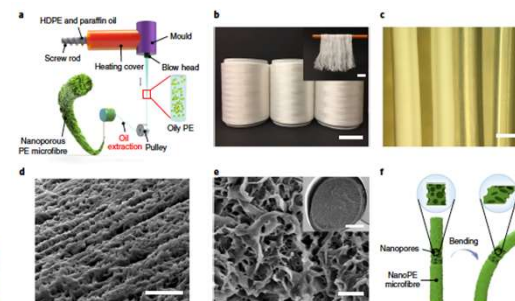
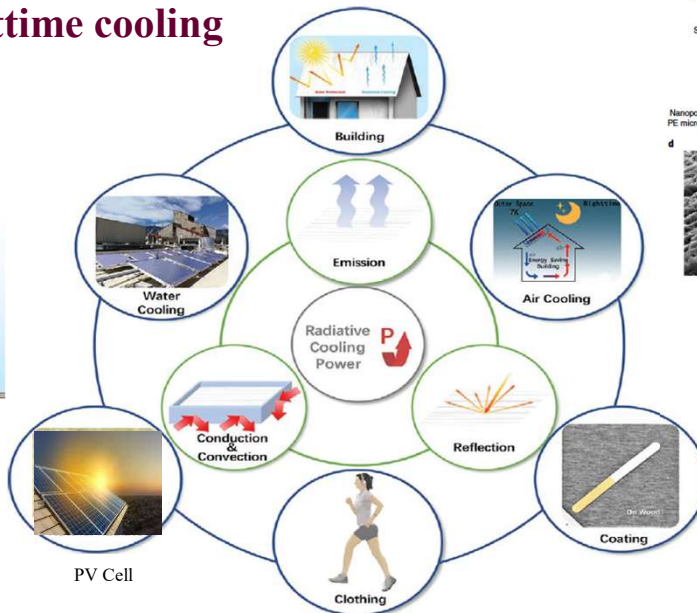
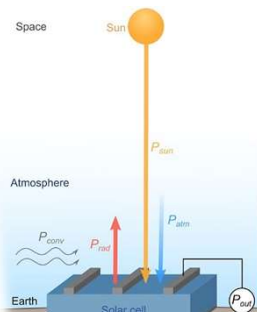
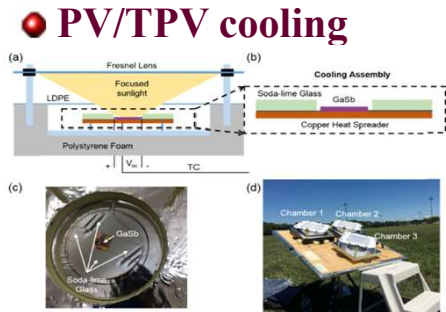
Applications

Multiple potential applications: daytime and nighttime cooling

Human body cooling

Y. Peng et al, Nature Sustainability, 1, 105 (2018).

PV/TPV cooling

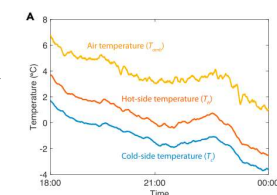
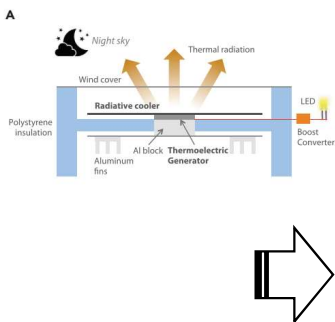


Z. ZHOU et al., Optics Express, 27, A404 (2019).

Enhancing thermoelectric generation

A. P. Raman et al., Joule, 3, 1 (2019).

Generating light from darkness!



Start-UP

Sky-cool

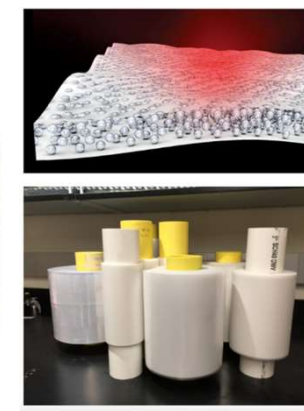


Aswath Raman
Co-Founder, Chief Science Officer
Aswath is a professor of Materials Science and Engineering at UCLA. He received his Ph.D. in Applied Physics from Stanford University and is passionate about improving the efficiency of energy systems.



Radi-cool

CEO: Ronggui Yang



Radiative cooling

J. Drévillon

● Challenges and perspectives

● Challenges

- Nanofabrication ➡ ➤ Transition to the industrial scale.
- Nano/micro porous structure and nanofibers ➡ ➤ Size control during elaboration (e.g electrospinning of different materials,...)
- Outdoor use: UV radiation / humidity / dust,...
- More precise models for the transparency of the atmosphere and the radiative flux from the environment.

● Perspectives

- Numerous proofs of concept: optimization and upscaling.
 - More generally: Optimization of the use of the cold darkness space!